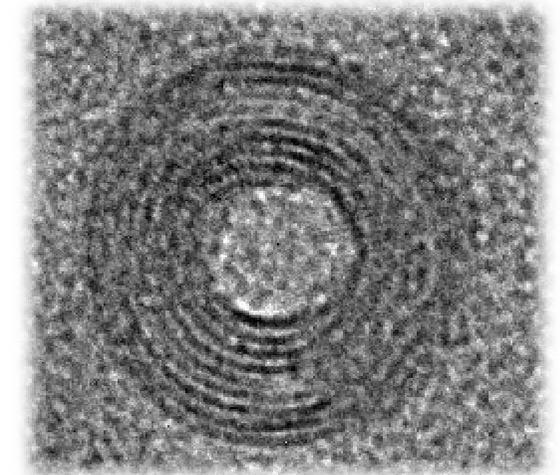


# Microstructure from diffraction: progress in line profile analysis

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[Matteo.Leoni@unitn.it](mailto:Matteo.Leoni@unitn.it)





# Foreword



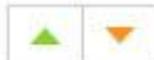
14.33 · 13.09 · National Institute of Technology

Rourkela

I don't believe it that the precision can't make the measurement to 0.00001Å with a x-ray wavelength of only 1.0Å.

That much precision will make the measurement to be unfaithful, who ever may do the measurement with whatever expertise in the field.

Such precision is also useless to express.



23 minutes ago

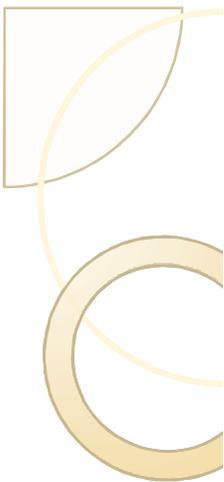
So people don't care/know about accuracy and precision....



How far from the truth?

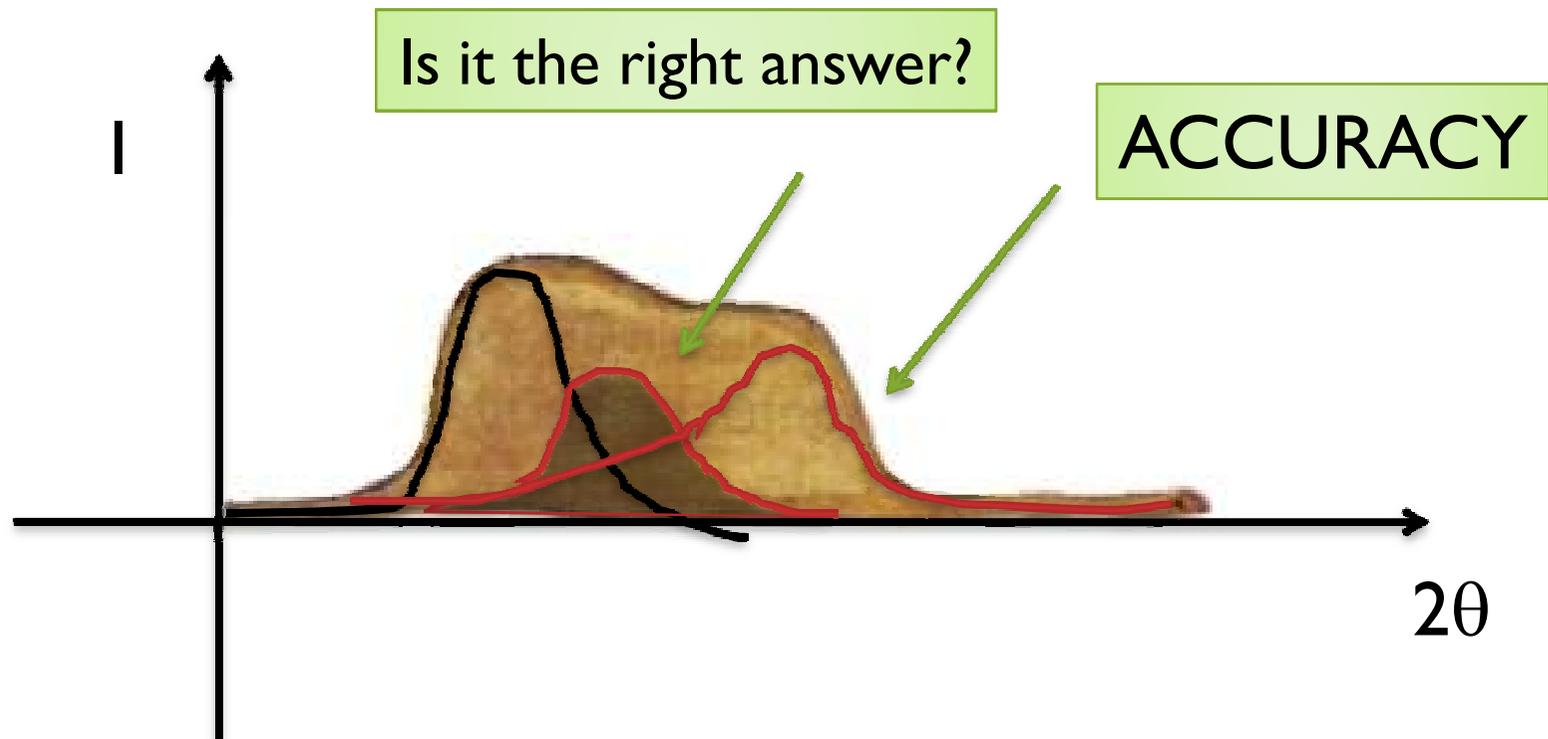


How many decimal places?



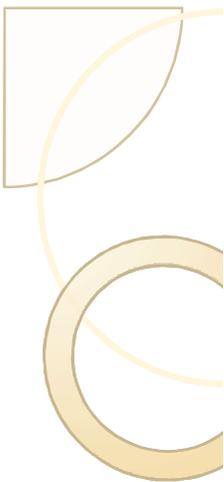
# Accuracy and microstructure

Are you frightened by this?

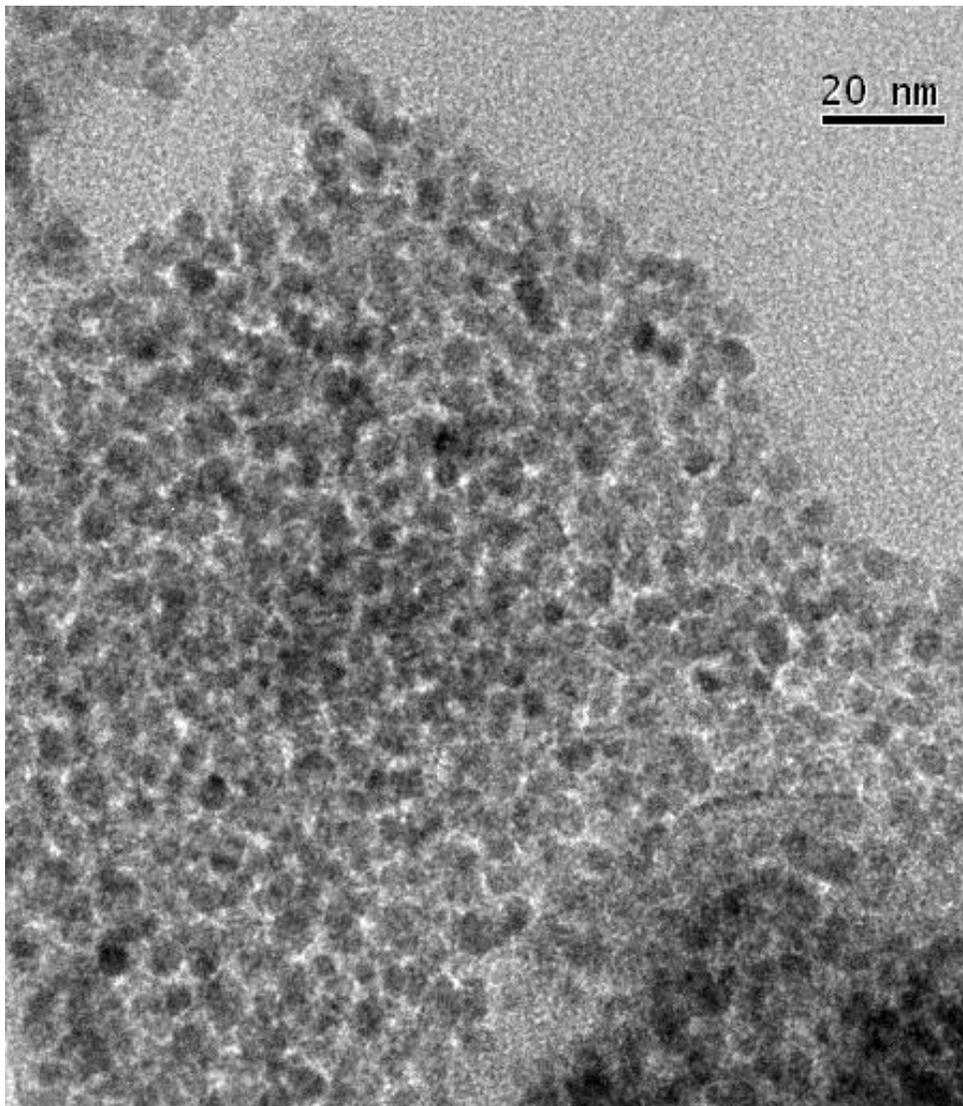


"Frighten? Why should any one be frightened by a hat?"

Antoine de Saint-Exupéry (1943) *The little prince*. Chapter 1

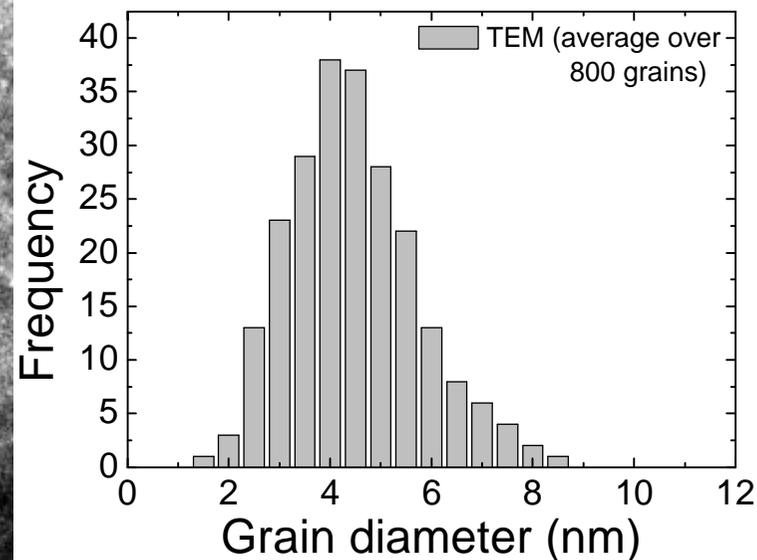


# Nanocrystalline ceria - TEM



CeO<sub>2</sub> calcinated at 400°C for 1h

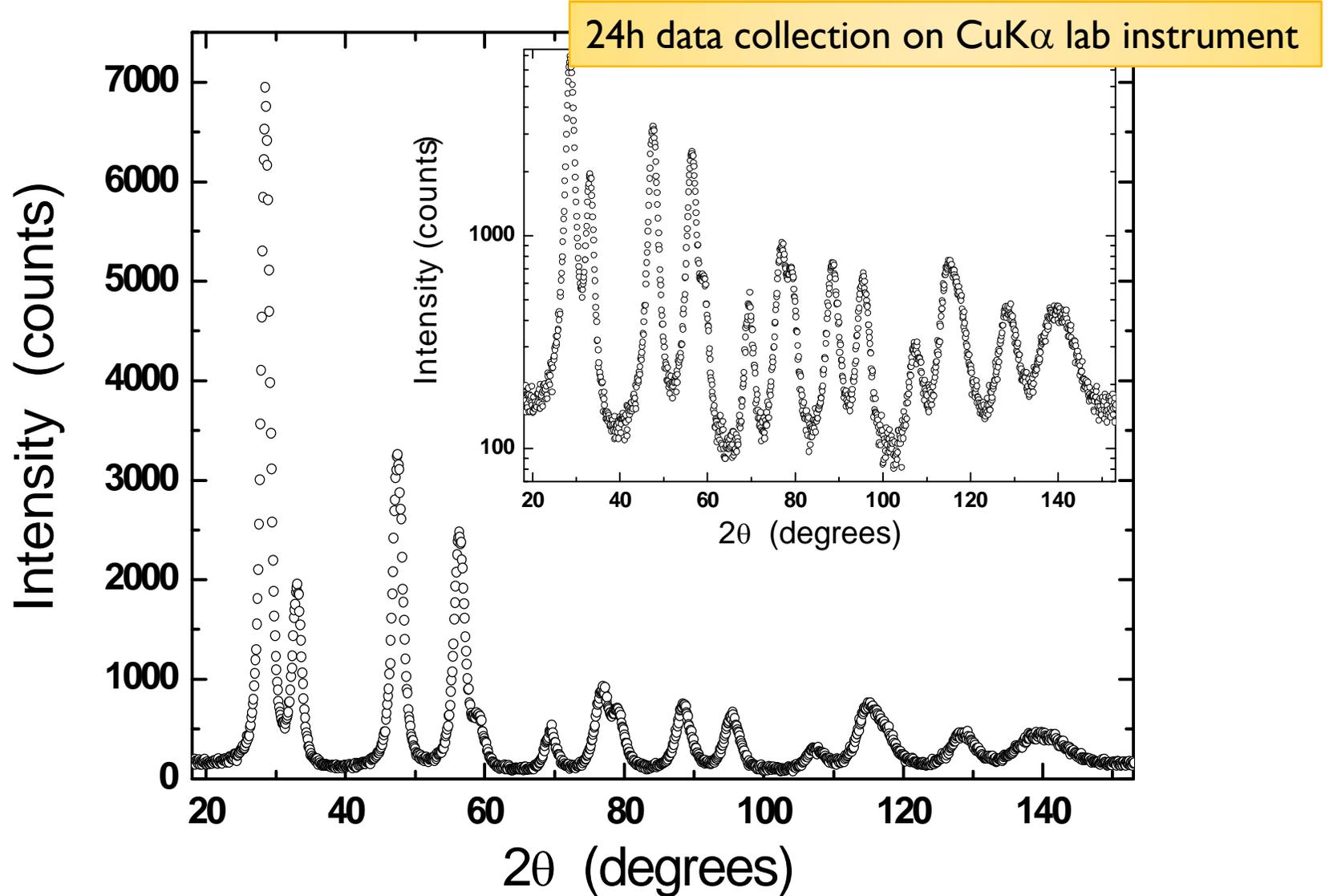
Grains are almost spherical and well separated



How does an XRD analysis result compare to this?



# Nanocrystalline ceria - XRD

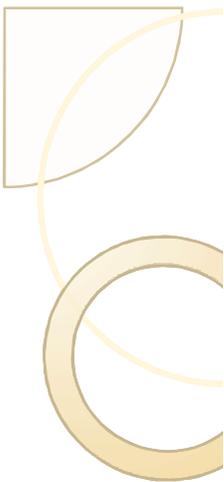


A high quality pattern is **NEEDED** to obtain accurate results



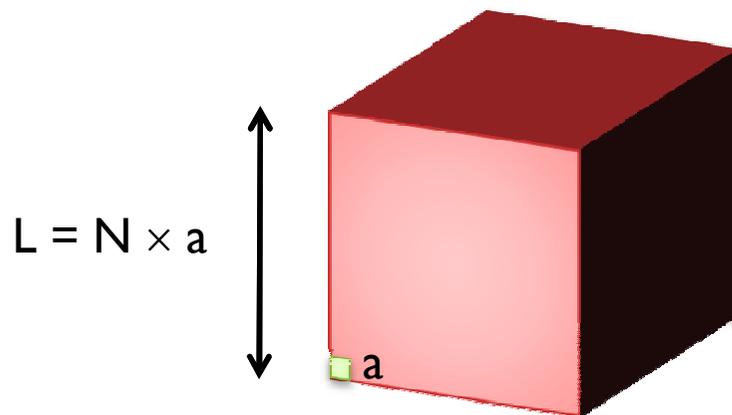
**HOW DO WE ANALYZE  
THE DATA?**

**OLD VS. NEW**



# 1918: Scherrer formula

Let's take a crystal of cube shape (edge  $L = N \times a$  where  $a$  is the unit cell size)



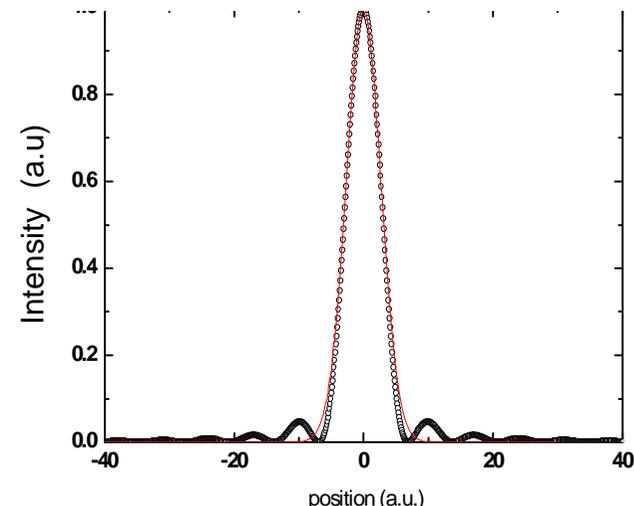
We have  $N^3$  cells in the cube

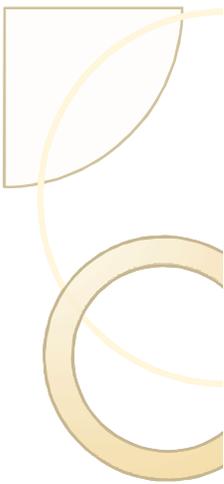
The diffracted intensity can be calculated in terms of trigonometric functions:

$$I_P \propto \frac{\sin(\pi N \Delta \mathbf{s} \cdot \mathbf{a} / \lambda)^2}{\sin(\pi \Delta \mathbf{s} \cdot \mathbf{a} / \lambda)^2} \frac{\sin(\pi N \Delta \mathbf{s} \cdot \mathbf{b} / \lambda)^2}{\sin(\pi \Delta \mathbf{s} \cdot \mathbf{b} / \lambda)^2} \frac{\sin(\pi N \Delta \mathbf{s} \cdot \mathbf{c} / \lambda)^2}{\sin(\pi \Delta \mathbf{s} \cdot \mathbf{c} / \lambda)^2}$$

conveniently approximated by **Gaussians**:

$$I_P \propto e^{-\pi \left( \frac{Na \Delta s}{\lambda} \right)^2} = e^{-\pi \left( \frac{Na \Delta (2\theta) \cos(\theta)}{\lambda} \right)^2}$$





# Scherrer formula

The **Full Width at Half Maximum (FWHM)** of the Gaussian is:

$$\frac{1}{2} = e^{-\pi \left( \frac{L \cos(\theta) \cdot FWHM}{2\lambda} \right)^2} \Rightarrow FWHM(2\theta) = \frac{2\lambda \sqrt{\ln(2)/\pi}}{L \cos(\theta)}$$

$$FWHM(2\theta) = \frac{0.94\lambda}{L \cos(\theta)}$$

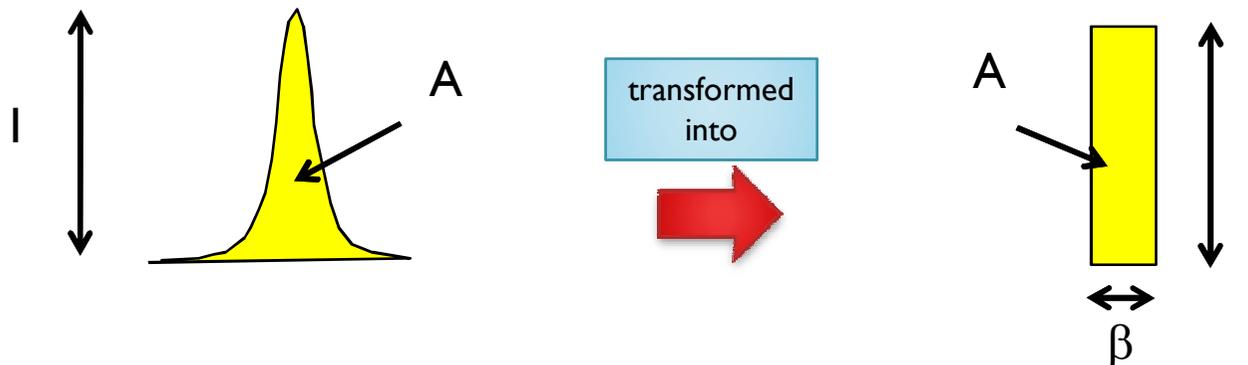
**Scherrer formula (1918)**

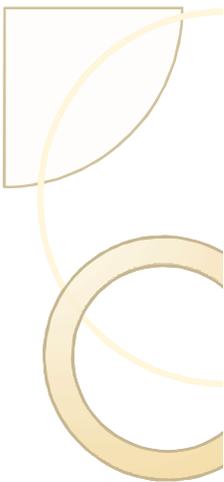
usually written as:

$$\beta_{hkl}(2\theta) = \frac{\lambda K_{\beta}}{\langle D \rangle_v \cos \theta_{hkl}}$$

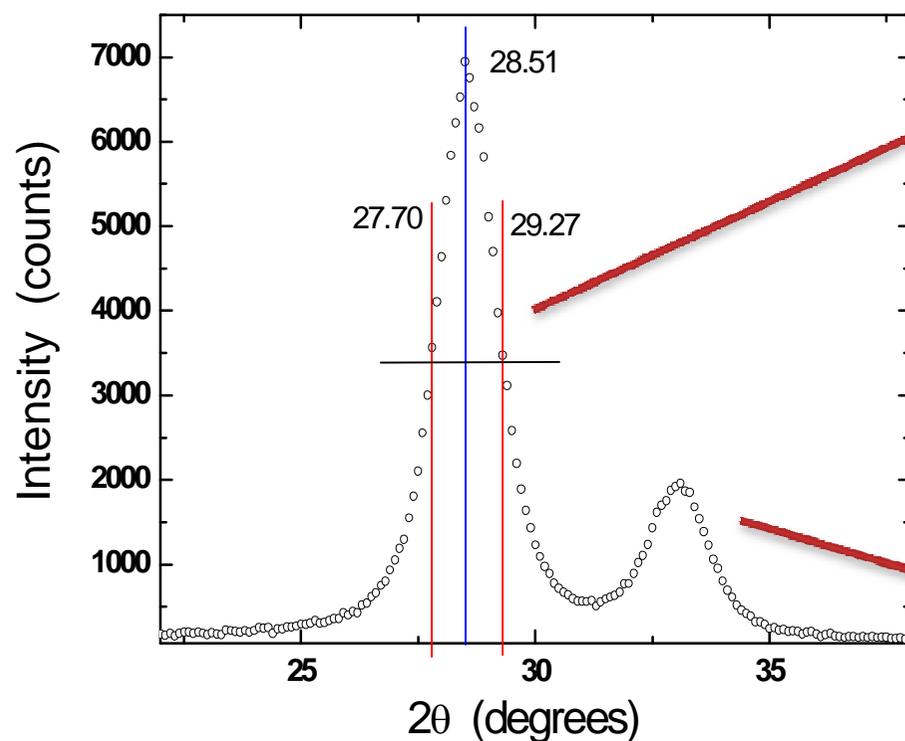
Any profile shape

in terms of Integral breadth  $\beta = A/I$  where A is the area and I the max intensity





# Scherrer formula (111) and (200) peaks



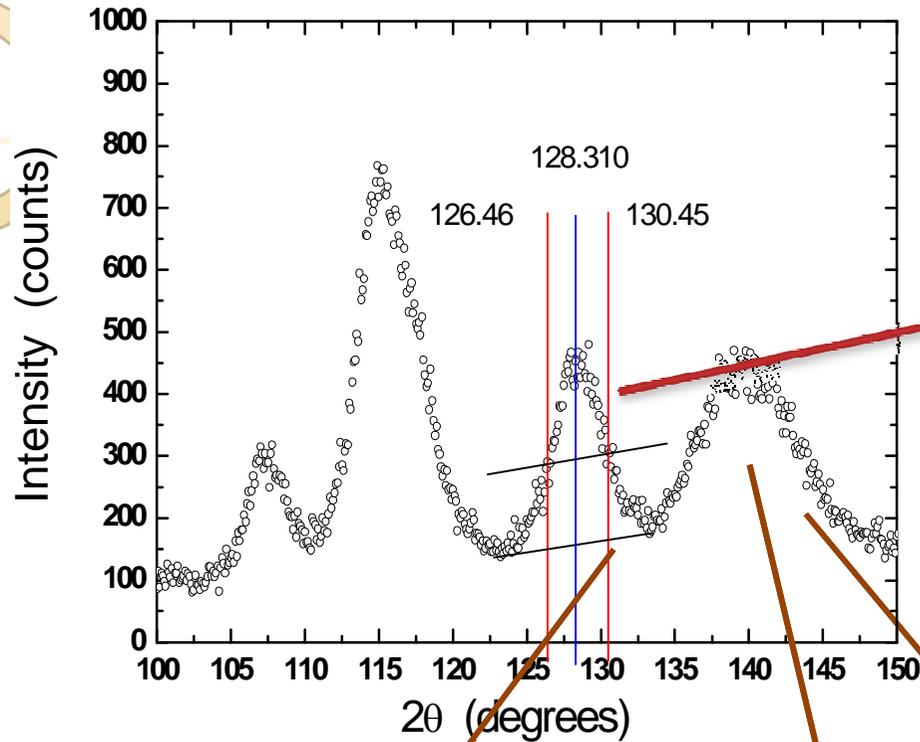
$$\left. \frac{\langle D \rangle_V}{K_\beta} \right|_{111} = 5.8 \text{ nm}$$

$$\left. \frac{\langle D \rangle_V}{K_\beta} \right|_{200} = 5.7 \text{ nm}$$

This is still applied by most “nanomaterials experts” in the literature

Formula obtained for GAUSSIAN/ANY peak and for a given shape of the domains (not yet decided)

# Scherrer formula (620) peak



$$\left. \frac{\langle D \rangle_V}{K_\beta} \right|_{620} = 5.1 \text{ nm}$$

How can we analyze those two peaks? Where is  $K\alpha_2$ ?

Why did we select this background shape/level?

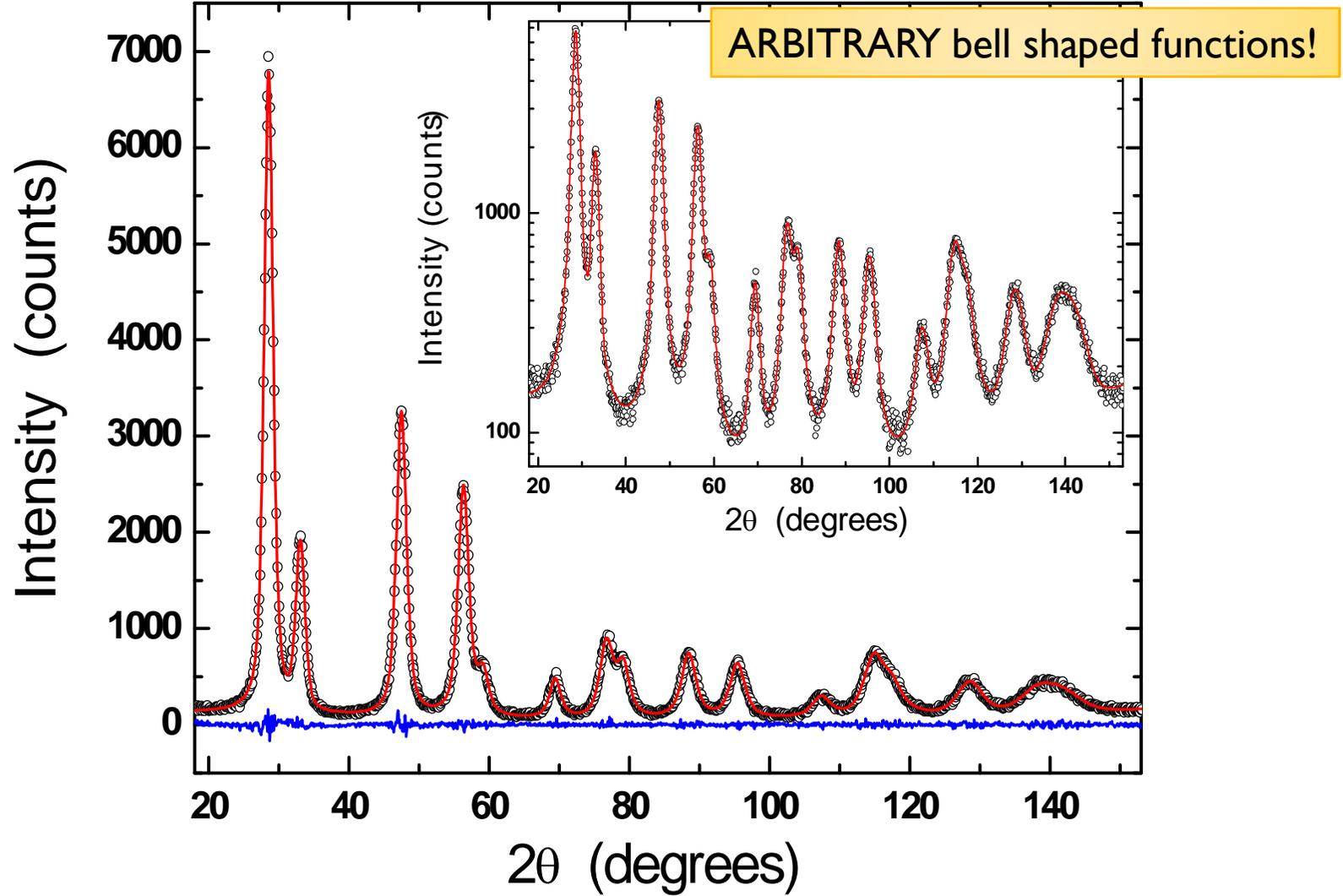
Does the instrument give no breadth contribution?

We have several different size values!



# Pattern decomposition

Accuracy in Powder Diffraction 4 – Gaithersburg 22-25 April 2013



Use of bell-shaped functions to account for superposition

# 1953: Williamson-Hall plot

Williamson-Hall plot includes Scherrer formula (1918) for “average size determination” with differential of Bragg law to get information on defects present in the material

$$\beta(d^*) = \frac{K_\beta}{\langle D \rangle_V} + 2 \cdot \langle \varepsilon^2 \rangle^{1/2} \cdot d^*$$

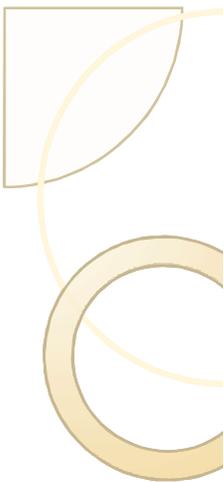
The  $\beta$  is the sum of the component only for Gaussian peaks

intercept related to “average domain size”

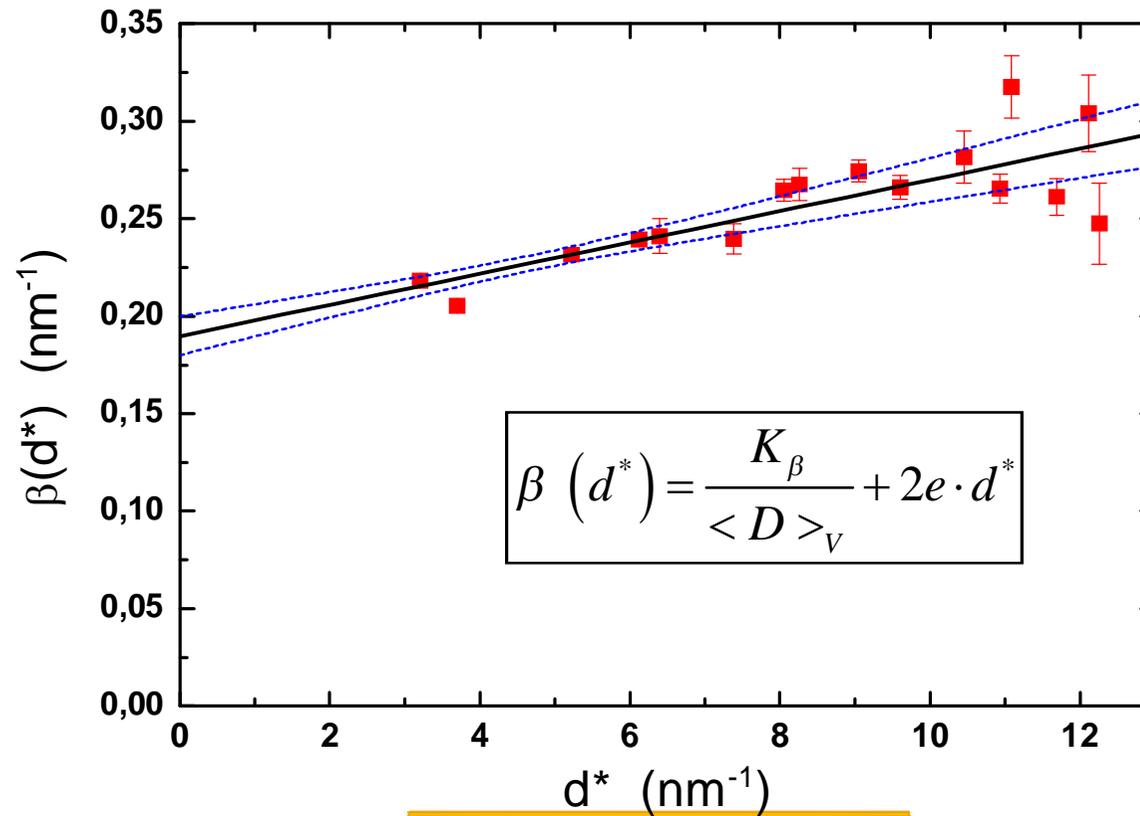
slope related to “microstrain”

$$0 = 2\Delta d \sin(\theta) + 2d \cos(\theta) \Delta\theta \quad \rightarrow \quad \Delta(2\theta) = -2 \frac{\Delta d}{d} \tan(\theta) = -2e \tan(\theta)$$

In a  $\beta(d^*)$  vs.  $d^*$  plot, intercept and slope of linear regression are related, respectively, to  $\langle D \rangle_V$  and  $e$



# Williamson-Hall plot



$$\beta(d^*) = 0.019 + 0.008d^*$$

$$\frac{\langle D \rangle_v}{K_\beta} = 5.3 \text{ nm}$$

$$e = \frac{0.008}{2} = 0.004$$

“average domain size” is NOT the average size of the (nano) particles  
“microstrain” is a quite general term and does not identify the defect types

# 1950: Warren-Averbach method

Actually, in RECIPROCAL SPACE the profile is a convolution of effects!

$$h(s) = \left[ f^{size}(s) \otimes f^{strain}(s) \right] \otimes g(s) \leftarrow \text{instrument}$$

Fourier transform

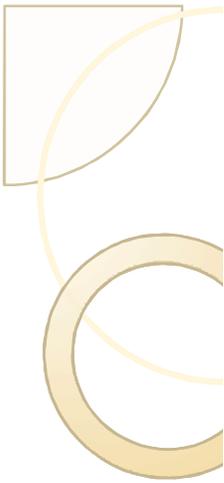
$$F(h(s)) = F(f^{size}(s)) F(f^{strain}(s)) F(g(s))$$

We can remove the known instrument effects

$$C(L) = A^{size}(L) A^{strain}(L)$$

We have a description of the profile(s) in Fourier space, from which:

$$\ln(C(L)) = \ln(A^{size}(L)) + \ln(A^{strain}(L))$$



# Warren-Averbach method

The strain term (related to displacement between couples) can be written as:

$$\begin{aligned} A^{strain}(L) &= \left\langle \cos\left(2\pi L \varepsilon_{hkl}(L) d_{hkl}^{*2}\right) \right\rangle \\ &= \left(1 - 2\pi^2 L^2 \left\langle \varepsilon_{hkl}^2(L) \right\rangle d_{hkl}^{*2} + O(L^4)\right) \end{aligned}$$

The first order approximation for the Fourier coefficients read

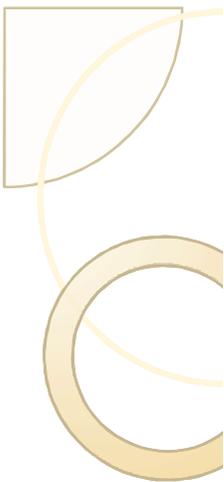
$$C(L) = A^{size}(L) \cdot \left(1 - 2\pi^2 L^2 \left\langle \varepsilon_{hkl}^2(L) \right\rangle h_0^2 / a^2\right)$$

Cubic case,  
but can be  
generalised

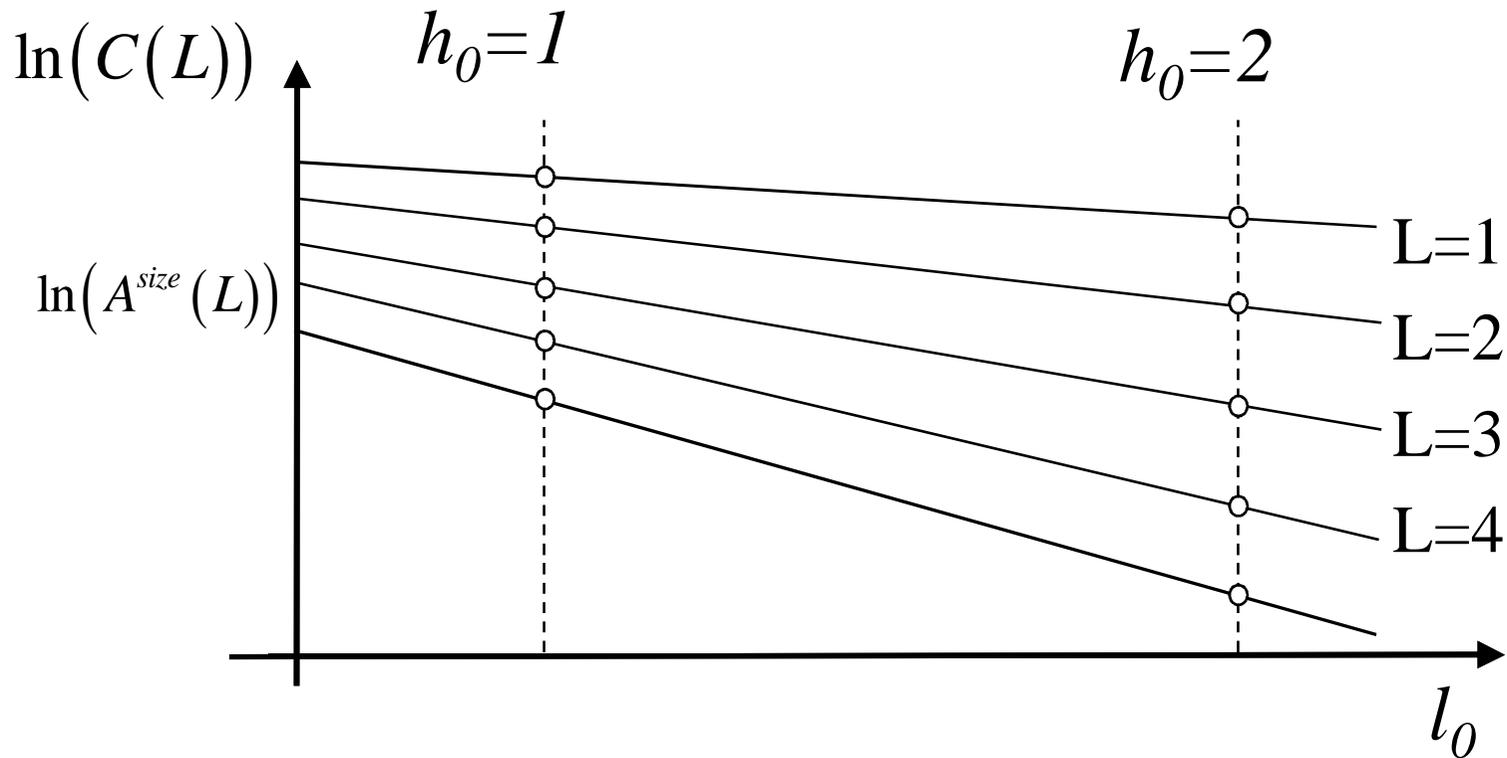
and then, taking the logarithm of both sides we obtain:

$$\ln(C(L)) = \ln(A^{size}(L)) - 2\pi^2 L^2 \left\langle \varepsilon_{hkl}^2(L) \right\rangle h_0^2 / a^2$$

Again linear plot gives size and strain contributions



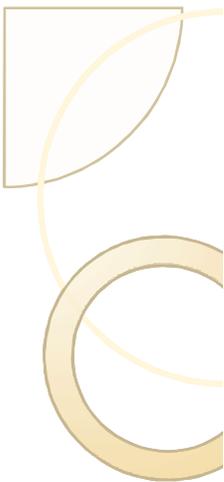
# Warren-Averbach method



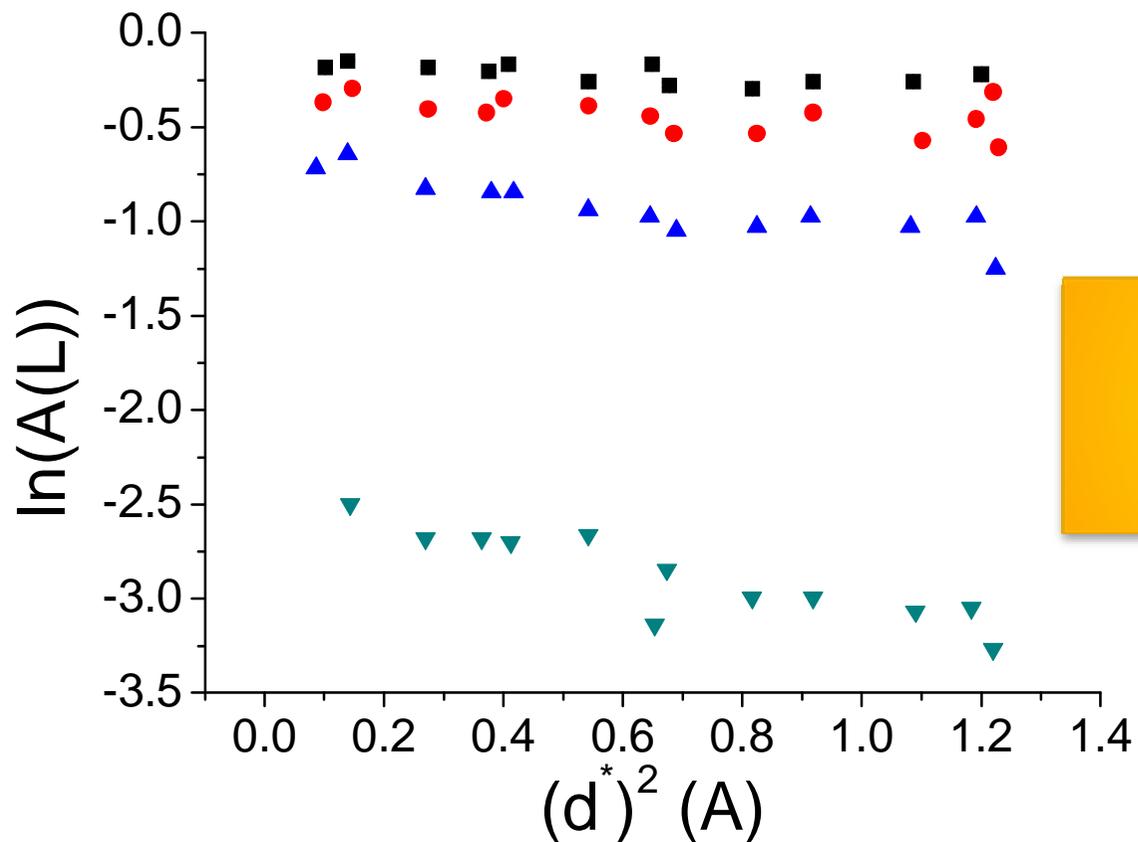
$$\ln(C(L)) = \ln(A^{size}(L)) - 2\pi^2 L^2 \langle \varepsilon_{hkl}^2(L) \rangle h_0^2 / a^2$$

intercept gives (INDIRECTLY)  
the size effect

slope gives DIRECTLY the strain  
effect

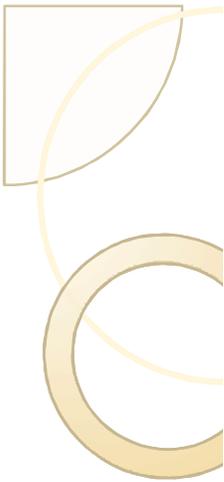


# Warren-Averbach plot



$$\langle D \rangle_s = 3.6 \text{ nm}$$

Taking the instrument into account, the value we obtain is much lower than the Round Robin one



# Warren-Averbach method

Provided that the procedure has been carried out properly (calculate Fourier Coefficients, account for background, instrumental component and peak overlapping, presence of faulting, other defects ...):

## Size coefficients

to be related to the column length distribution  $p(L) \propto d^2 A^{size}(L) / dL^2$

## So-called “Microstrain”

$$\langle \varepsilon_{hkl}^2(L) \rangle^{1/2}$$

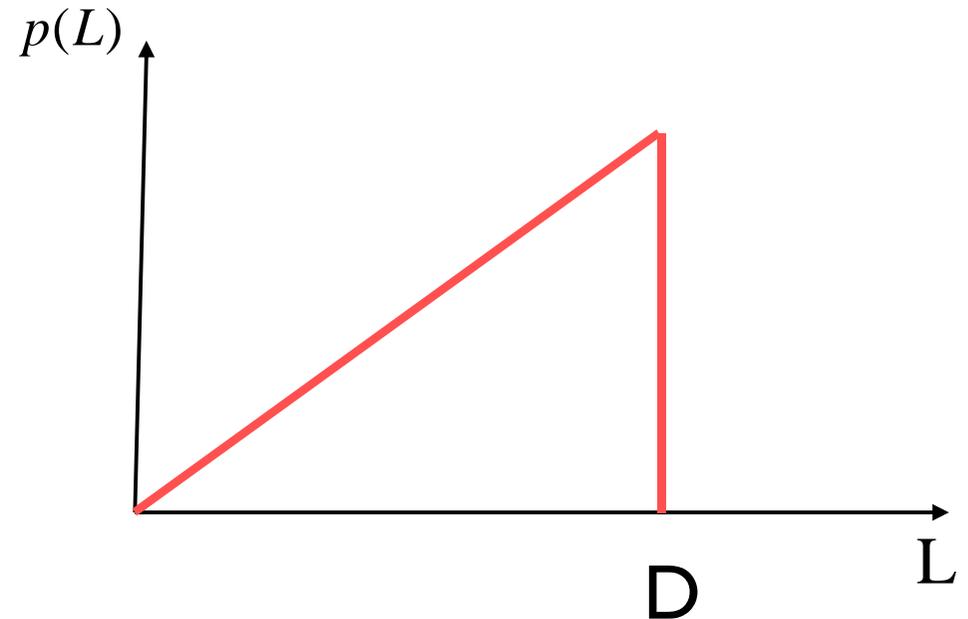
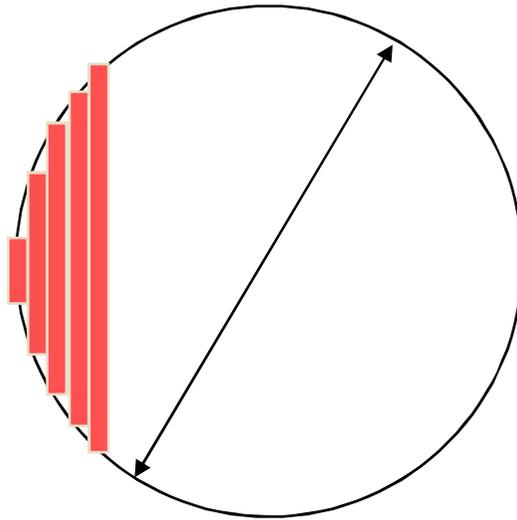
to be related to the strain distribution  $p(\varepsilon_{hkl}(L))$  generated by the specific source of lattice strain)

WHICH column length distribution?

Microstrain is NOT a strain!!!! WHICH source of lattice strain?

# Meaning of the size term

Column length distribution.... e.g. for a single sphere:



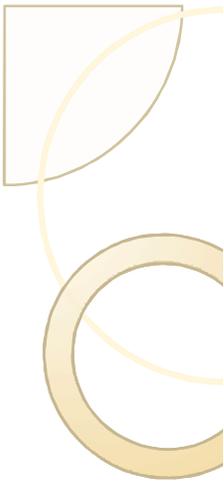
..and for a distribution of domains

$$\langle L \rangle_v = \frac{\langle D \rangle_v}{K_\beta} = \frac{M_4}{M_3 \cdot K_\beta} = \int D^4 p(D) dD / \int D^3 p(D) dD$$

Williamson-Hall

$$\langle L \rangle_s = \frac{\langle D \rangle_s}{K_\kappa} = \frac{M_3}{M_2 \cdot K_\kappa} = \int D^3 p(D) dD / \int D^2 p(D) dD$$

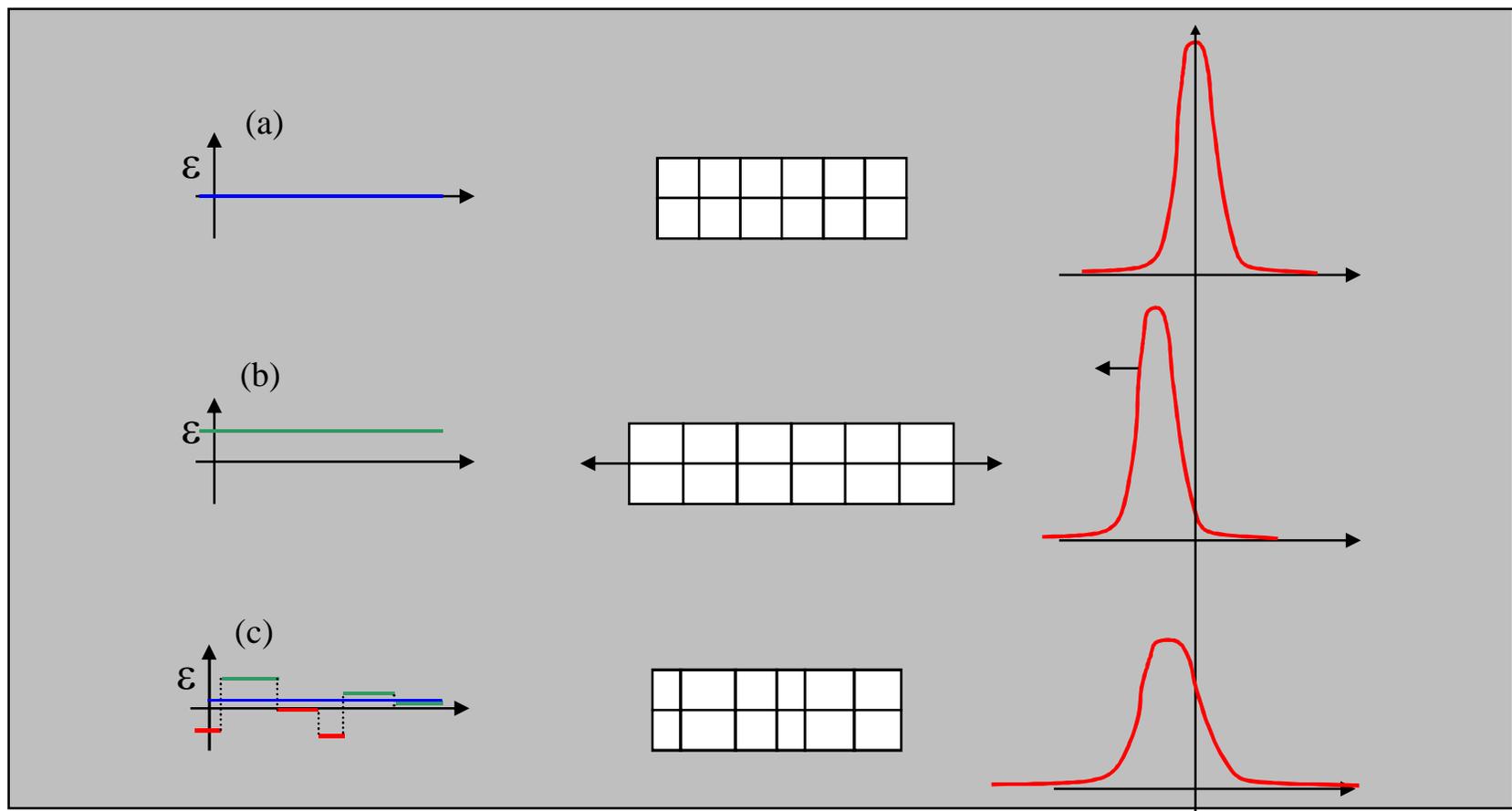
Warren-Averbach



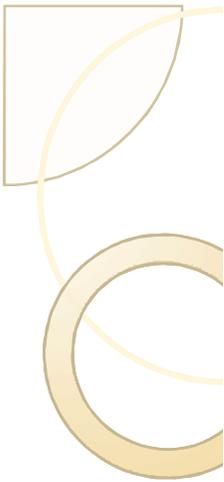
# Meaning of strain (distortion) term

When the deformation is non uniform, we can introduce the microstrain

$$\langle \varepsilon^2 \rangle^{1/2} = \langle (\Delta d/d)^2 \rangle^{1/2}$$

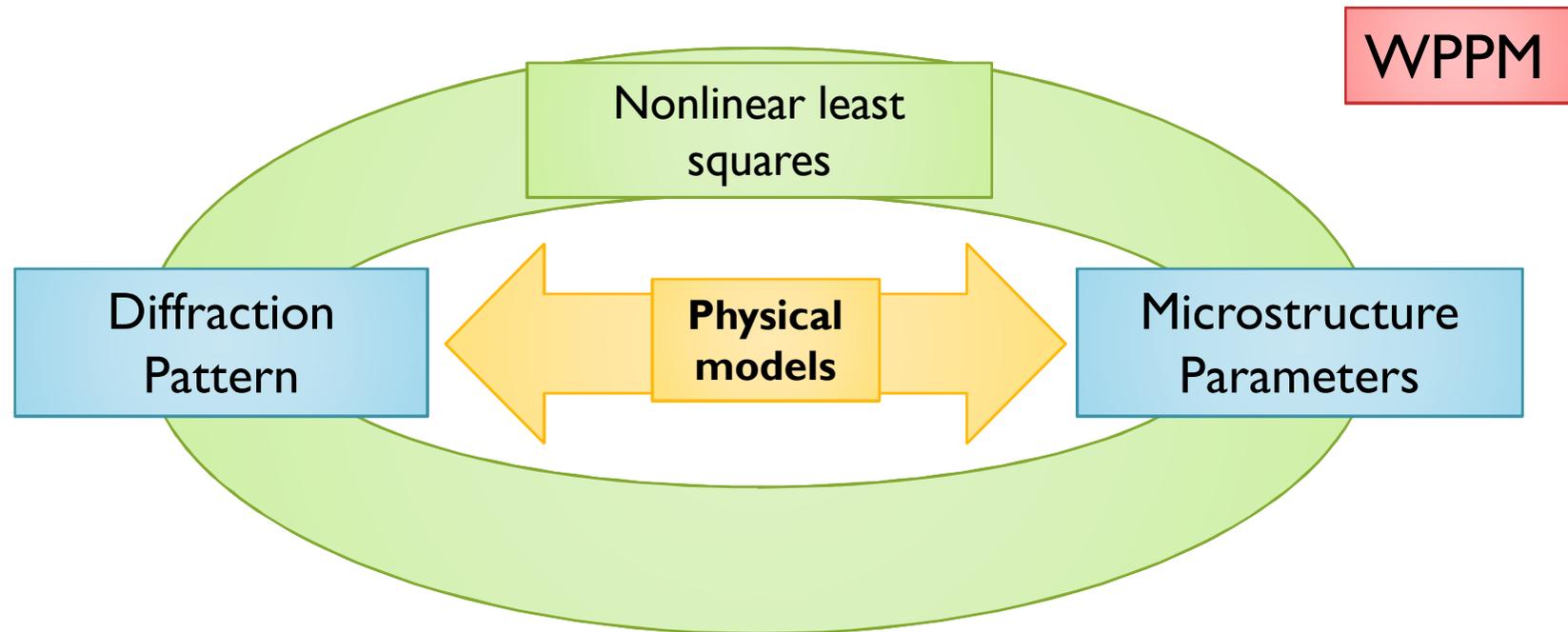


**MICROSTRAIN is NOT a strain!!!!**



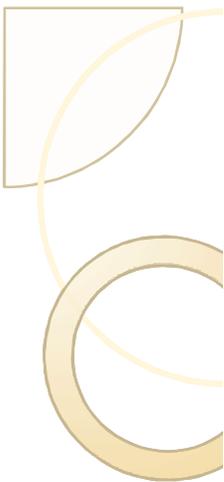
# 2000: Whole Powder Pattern Modelling

Instead of doing a deconvolution, we directly model the whole pattern in terms of physical models of the microstructure:



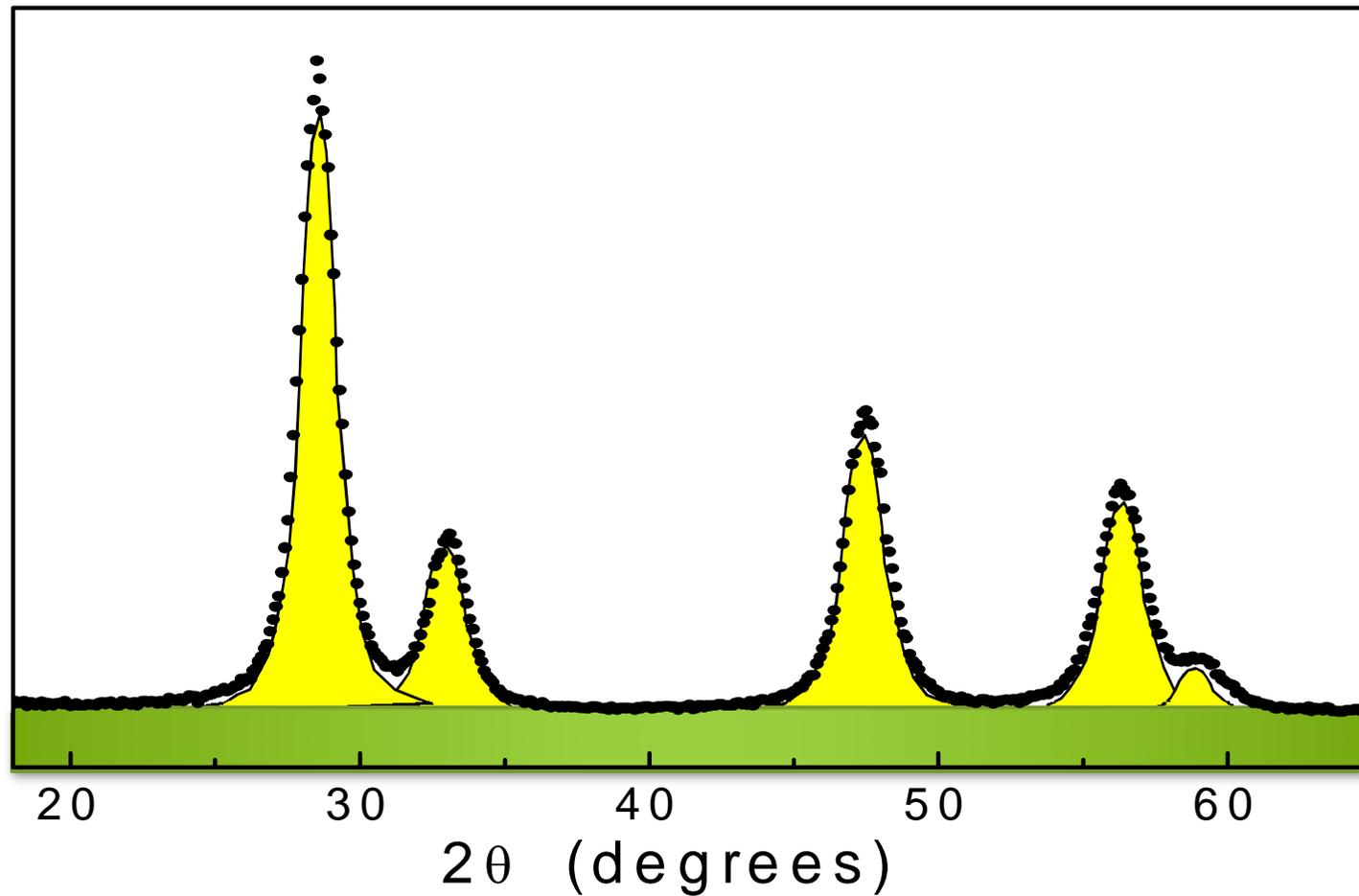
Self-consistent one-step procedure: we work on the measured data!

Structure is decoupled from microstructure, i.e. **there are no structural constraints (peak intensity is a fitting parameter)**.



# WPPM basics

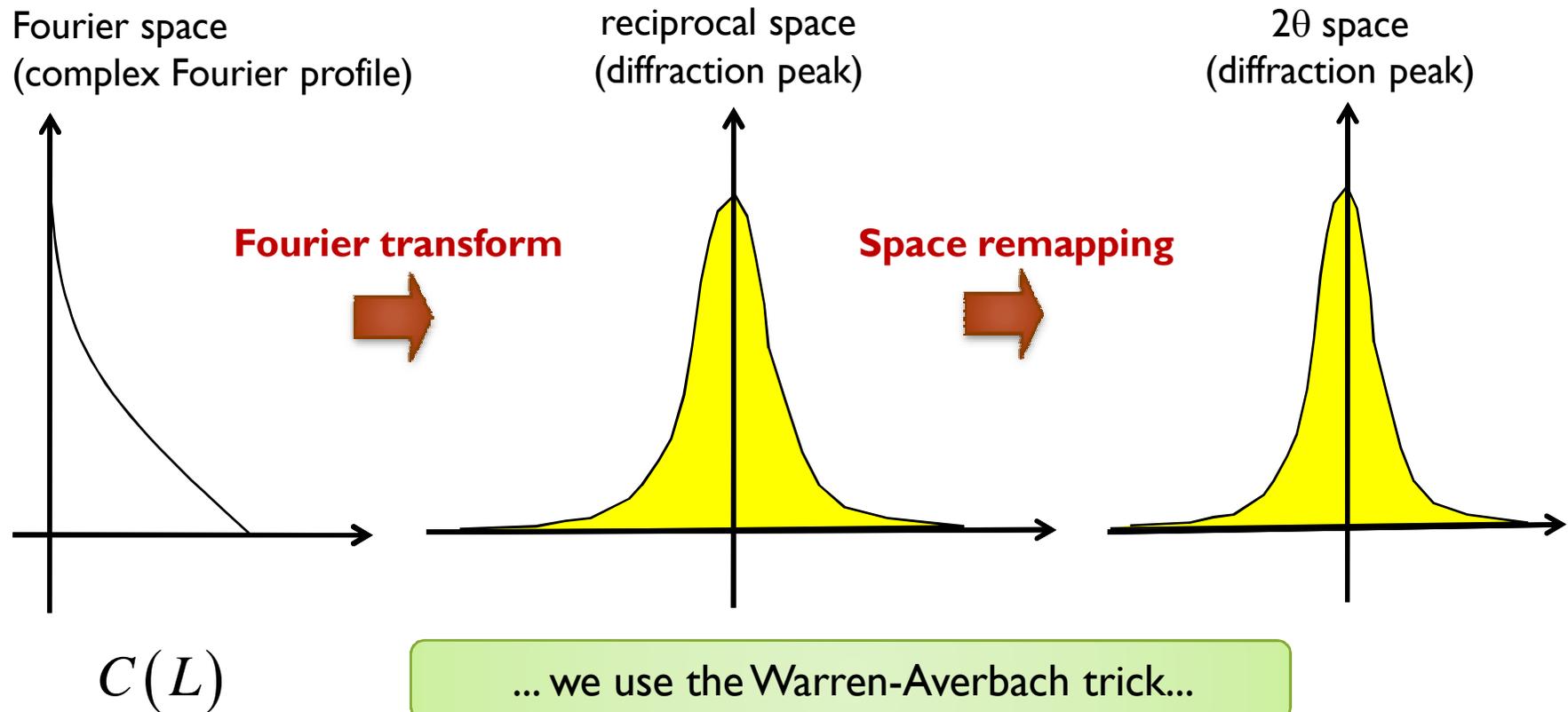
Pattern as sum of broadened peaks + background + ...



...a kind of “Pawley” or “Rietveld-like” approach... **BUT**....

# WPPM basics

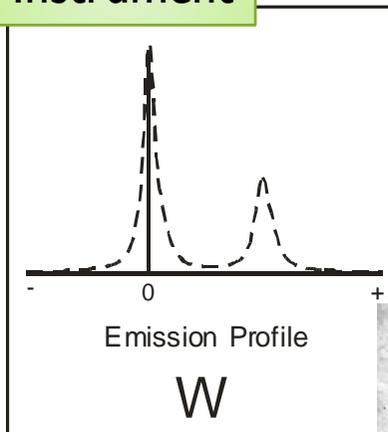
Each profile synthesised (in reciprocal space) from its Fourier transform calculated by physical modelling of all broadening sources



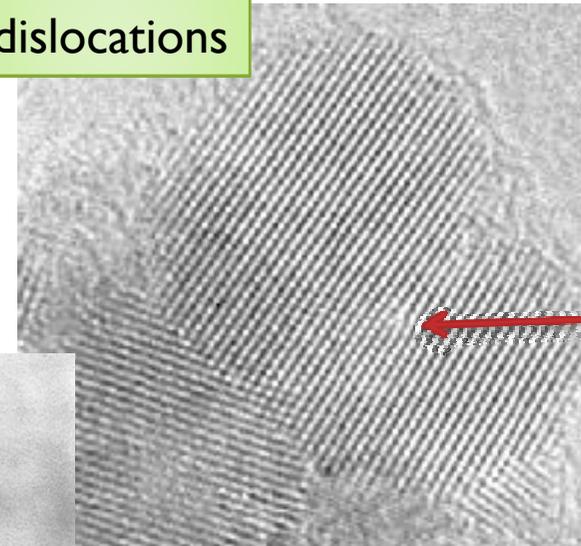
# WPPM basics

## Broadening sources

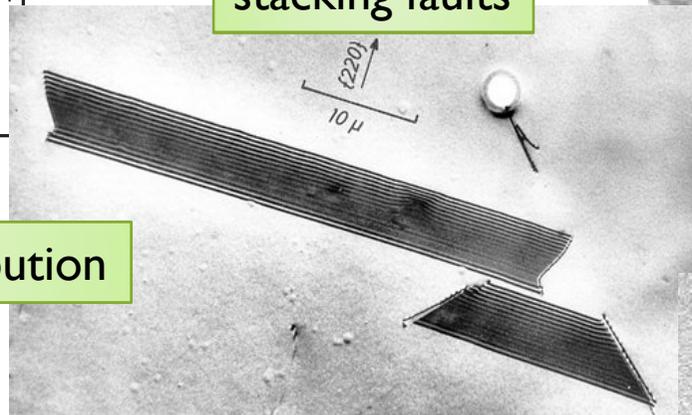
Instrument



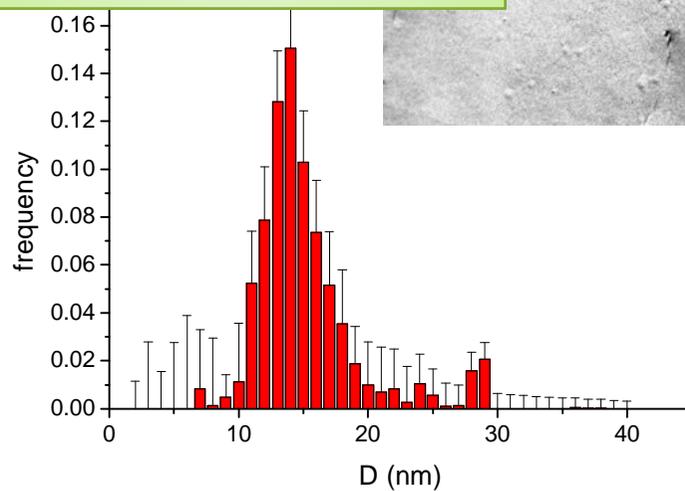
dislocations



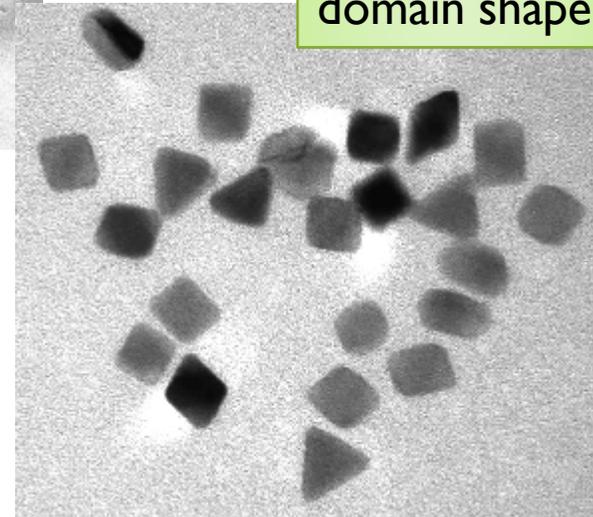
stacking faults



domain-size distribution



domain shape



# WPPM: plug and play

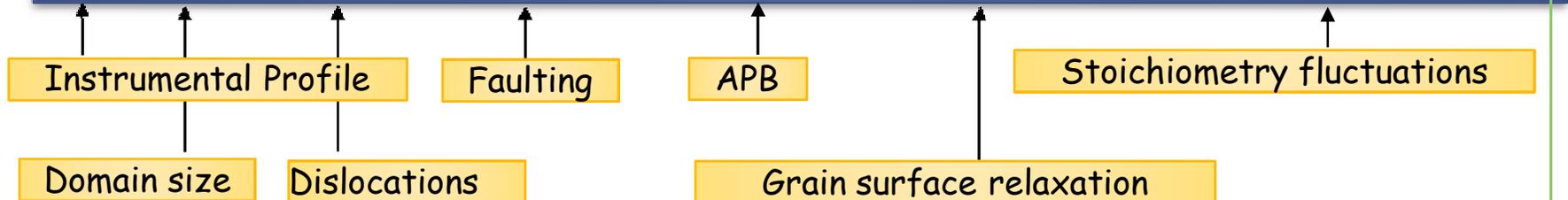
The intensity is obtained as Fourier transform of the global broadening function:

$$I_{\{hkl\}}(d^*, d_{\{hkl\}}^*) = k(d^*) \cdot \sum_{hkl} w_{hkl} \int_{-\infty}^{\infty} \mathbb{C}_{hkl}(L) \exp(2\pi i L \cdot s_{hkl}) dL$$

Profile in reciprocal space

Profile in Fourier space

$$T_{pV}^{IP} \cdot A_{\{hkl\}}^S \cdot A_{\{hkl\}}^D \cdot (A_{hkl}^F + iB_{hkl}^F) \cdot A_{\{hkl\}}^{APB} \cdot (A_{hkl}^{GSR} + iB_{hkl}^{GSR}) \cdot (A_{hkl}^{CF} + iB_{hkl}^{CF}) \cdot \dots$$



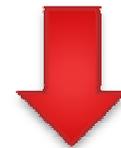
Additional line broadening sources can be included through the corresponding FTs

We have a fingerprint of the microstructure

# General dislocation model

Wilkins model for dislocation-related broadening extended to any symmetry

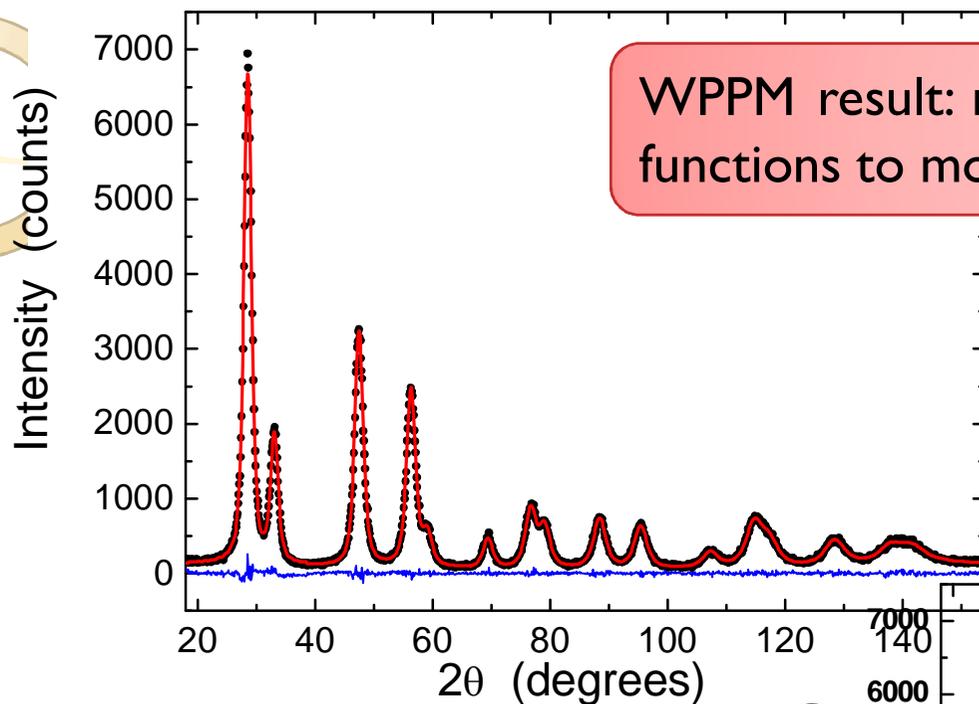
$$A_{\{hkl\}}^D(L) = \exp \left[ -\frac{\pi |b|^2}{2} \text{Inv}(E_1 \dots E_{15}, h, k, l) \rho d_{\{hkl\}}^{*2} L^2 f^*(L/R'_e) \right]$$



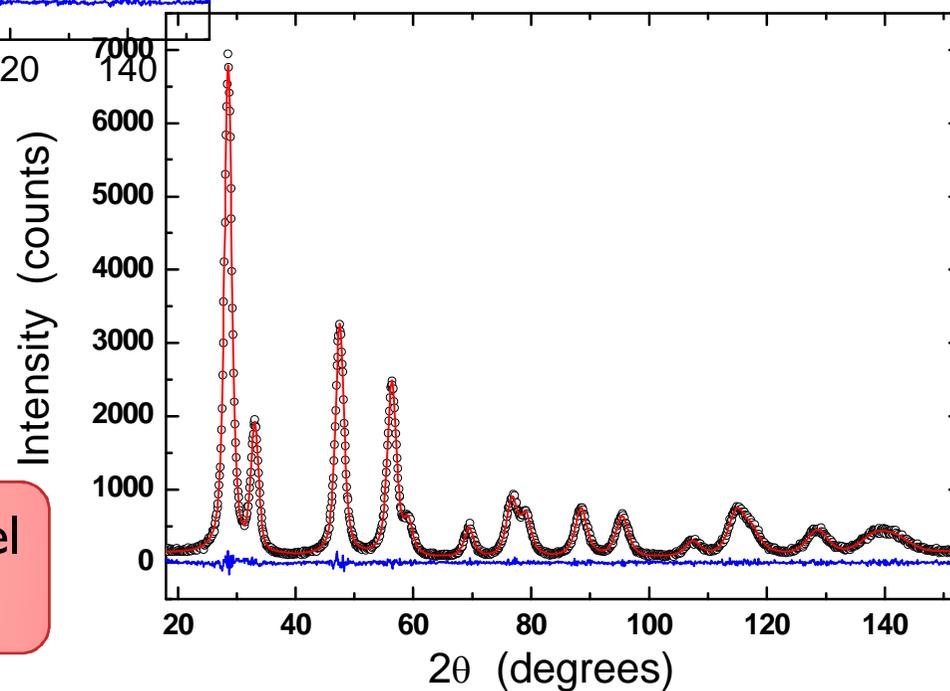
$$\begin{aligned} & \left[ E_1 h^4 + E_2 k^4 + E_3 l^4 + 2(E_4 h^2 k^2 + E_5 k^2 l^2 + E_6 h^2 l^2) + \right. \\ & + 4(E_7 h^3 k + E_8 h^3 l + E_9 k^3 h + E_{10} k^3 l + E_{11} l^3 h + E_{12} l^3 k) + \\ & \left. + 4(E_{13} h^2 kl + E_{14} k^2 hl + E_{15} l^2 hk) \right] / d_{\{hkl\}}^4 \end{aligned}$$

Coefficients **calculated** from slip system and single-crystal elastic constants or refined on the data (in this last case the meaning of  $\rho$  is watered down)

# Nano CeO<sub>2</sub> - WPPM

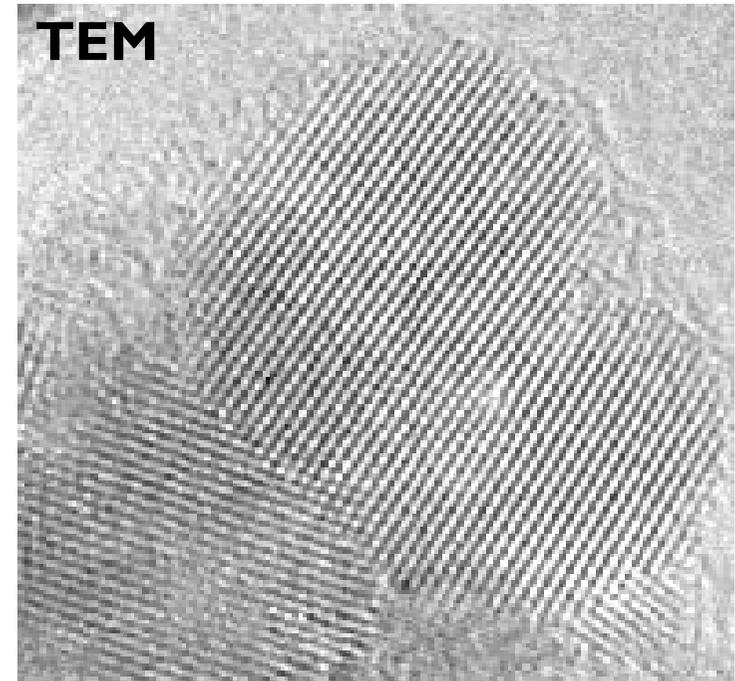
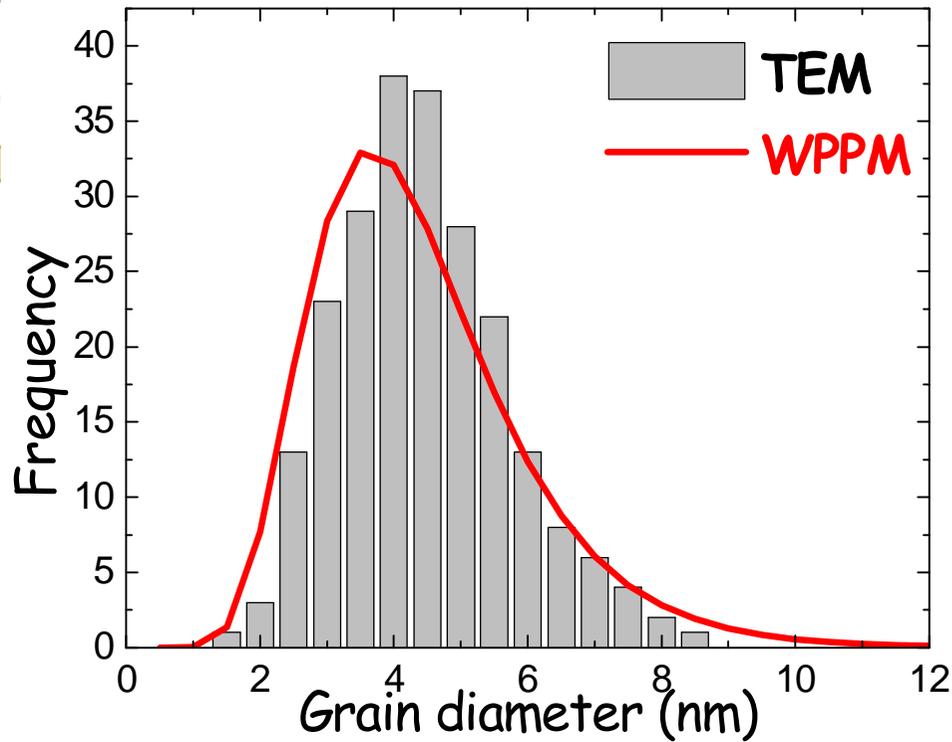


WPPM result: no Voigt or bell shaped arbitrary functions to model the data, 29 par, GoF 1.03



Pseudo-Voigt profiles to model the data, 70 par, GoF 1.01

# Nano CeO<sub>2</sub> – WPPM vs TEM



$\rho \approx 1.4(9) \cdot 10^{16} \text{ m}^{-2}$   
ca. 1 dislocation every 3-4 grains

$\langle D \rangle = 4.4 \text{ nm}$

We just assumed a lognormal distribution of spheres with dislocations on the primary slip system



# Ceria summary

$$\frac{\langle D \rangle_v}{K_\beta} = 5.3 \text{ nm}$$

Williamson-Hall

$$\langle D \rangle_s = 3.6 \text{ nm}$$

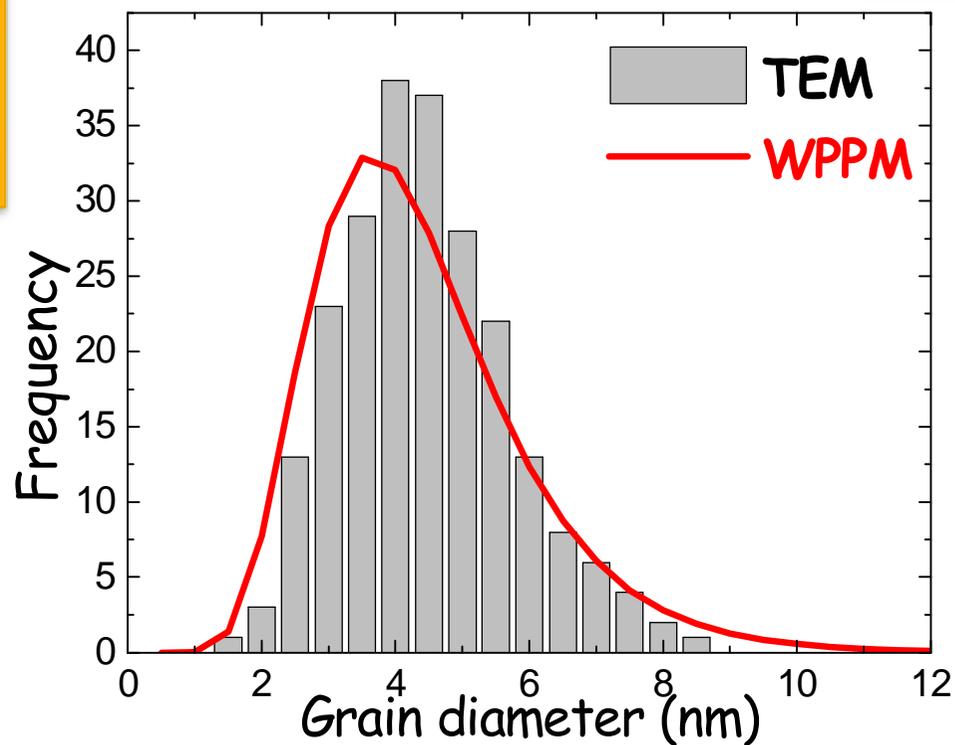
Warren-Averbach

WPPM

$$\langle D \rangle = 4.4(2) \text{ nm}$$

$$\frac{\langle D \rangle_v}{K_\beta} = 5.1 - 5.8 \text{ nm}$$

Scherrer

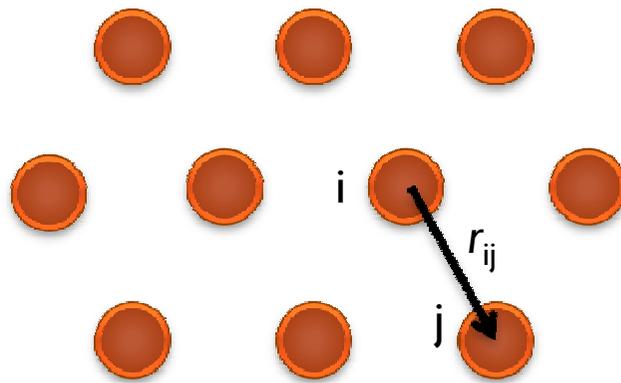




# **FURTHER ACCURACY PROBLEMS**

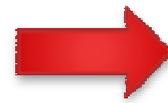
# WPPM versus Debye equation

The Debye equation links atomic coordinates and diffraction pattern:



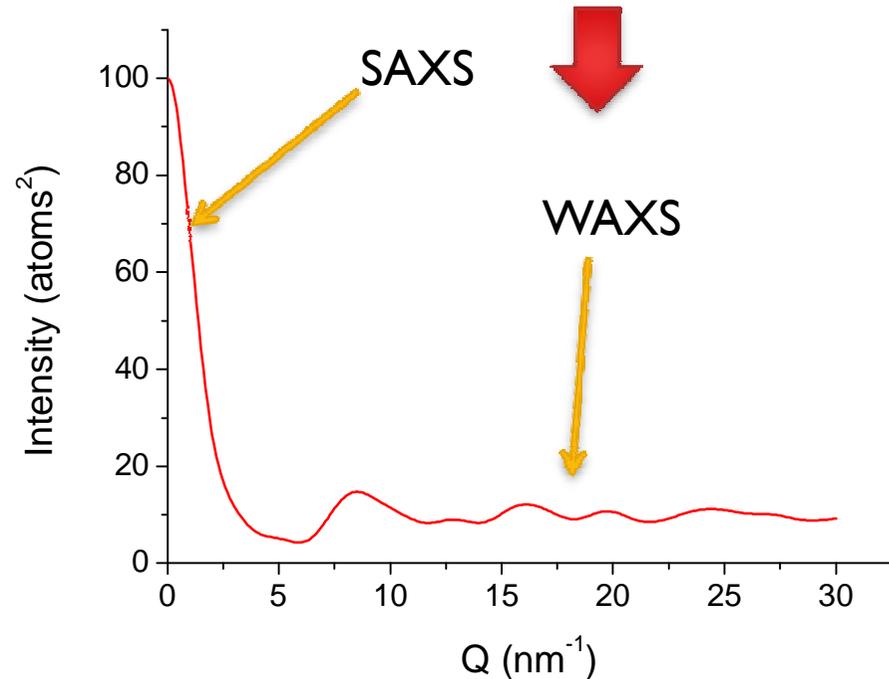
$$Q = \frac{4\pi \sin \theta}{\lambda}$$

SAXS is in the ideally diluted limit



$$I(Q) \propto \sum_i^N \sum_j^N \text{sinc}(\mathbf{r}_{ij} \cdot \mathbf{Q})$$

The formula gives directly the powder diffraction pattern in reciprocal space



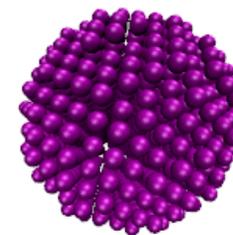
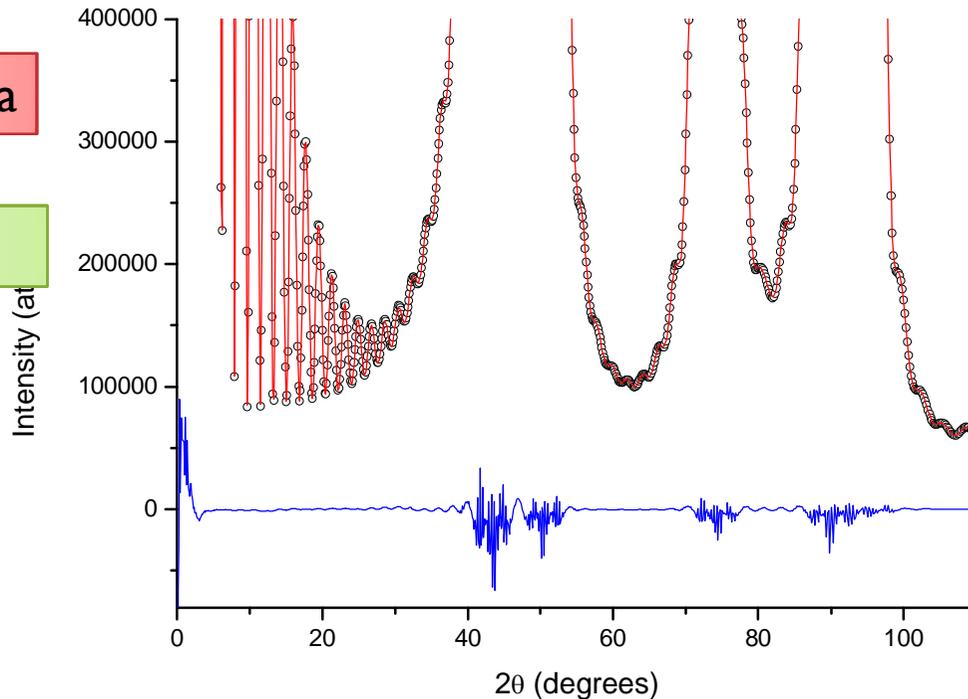
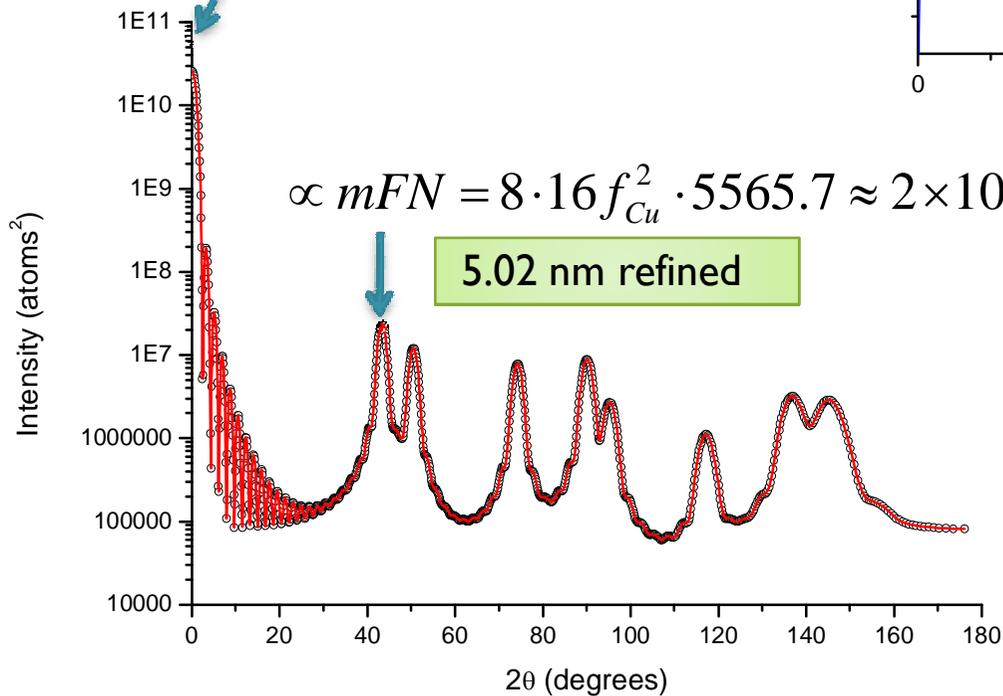
# WPPM versus Debye equation

single 5 nm Cu domain, CuK<sub>α</sub> data

atoms: 5565.7 vs 5566 simulated

$$I(0) = f_{Cu}^2 N^2 \approx 2.6 \times 10^{10}$$

5.00 nm refined

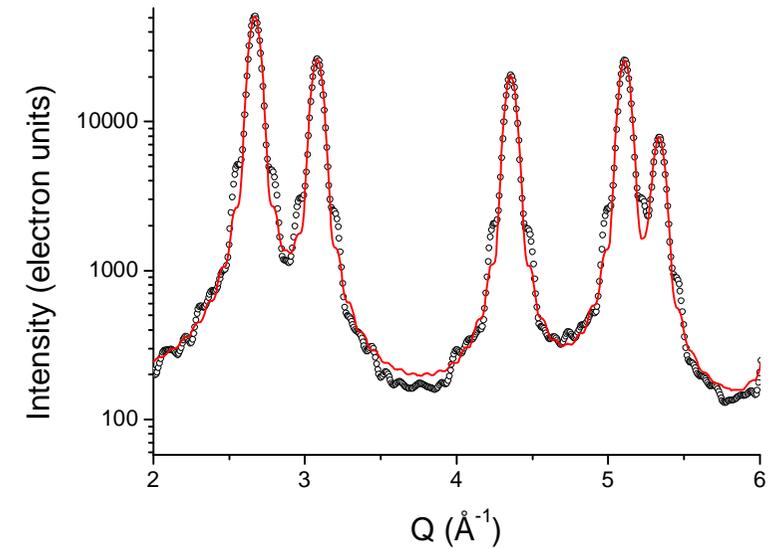
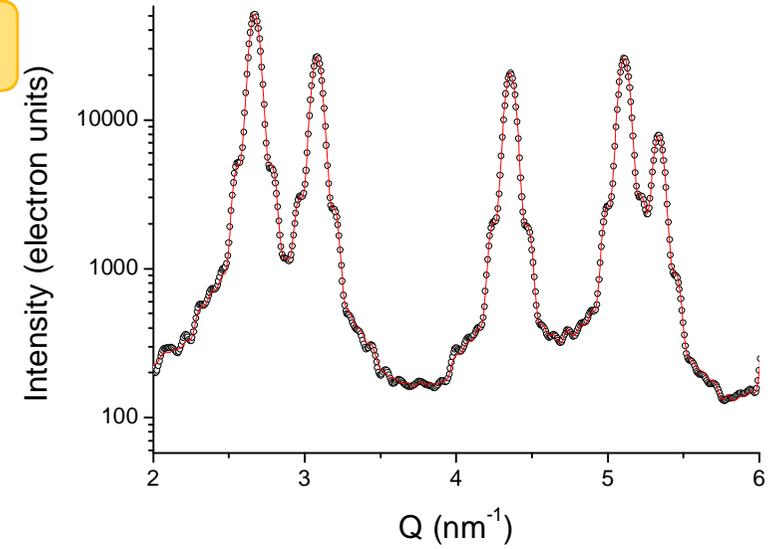
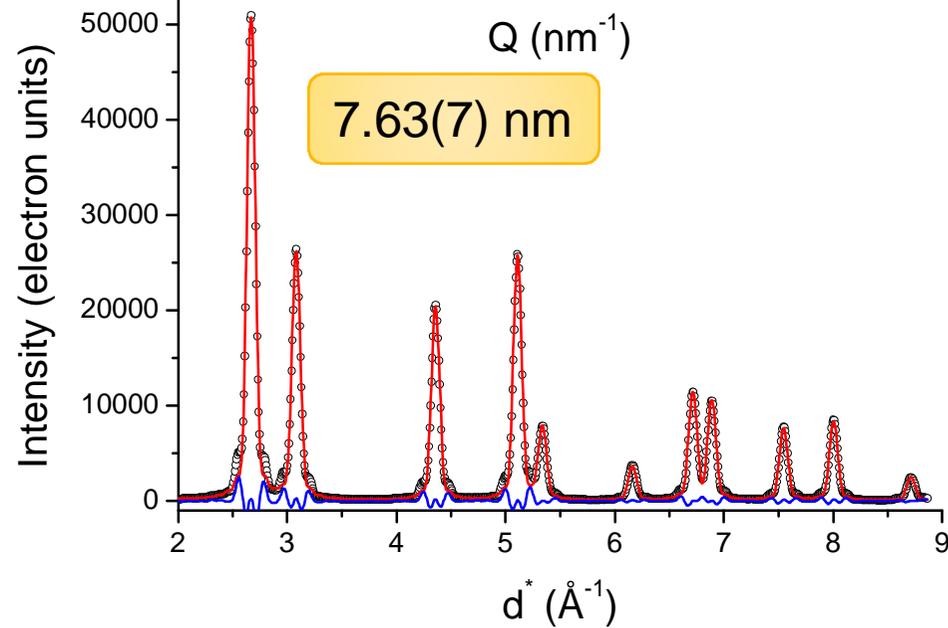
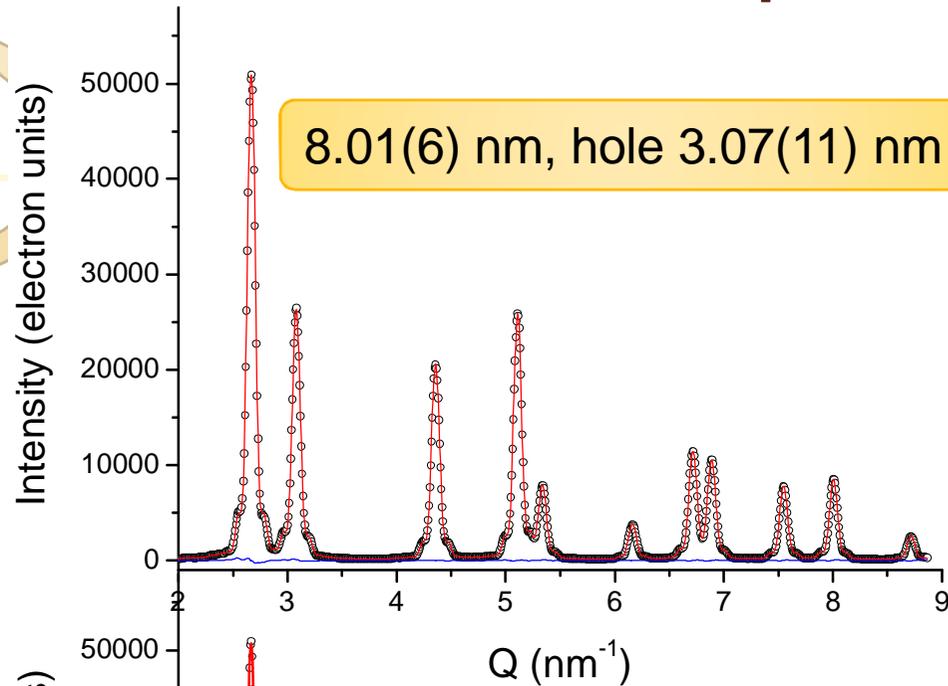


SAXS (sphere)  
 WPPM (sphere)  
 Warren intensity formula  
 Patterson sphere correction



# Hollow 8nm Au sphere (3nm hole)

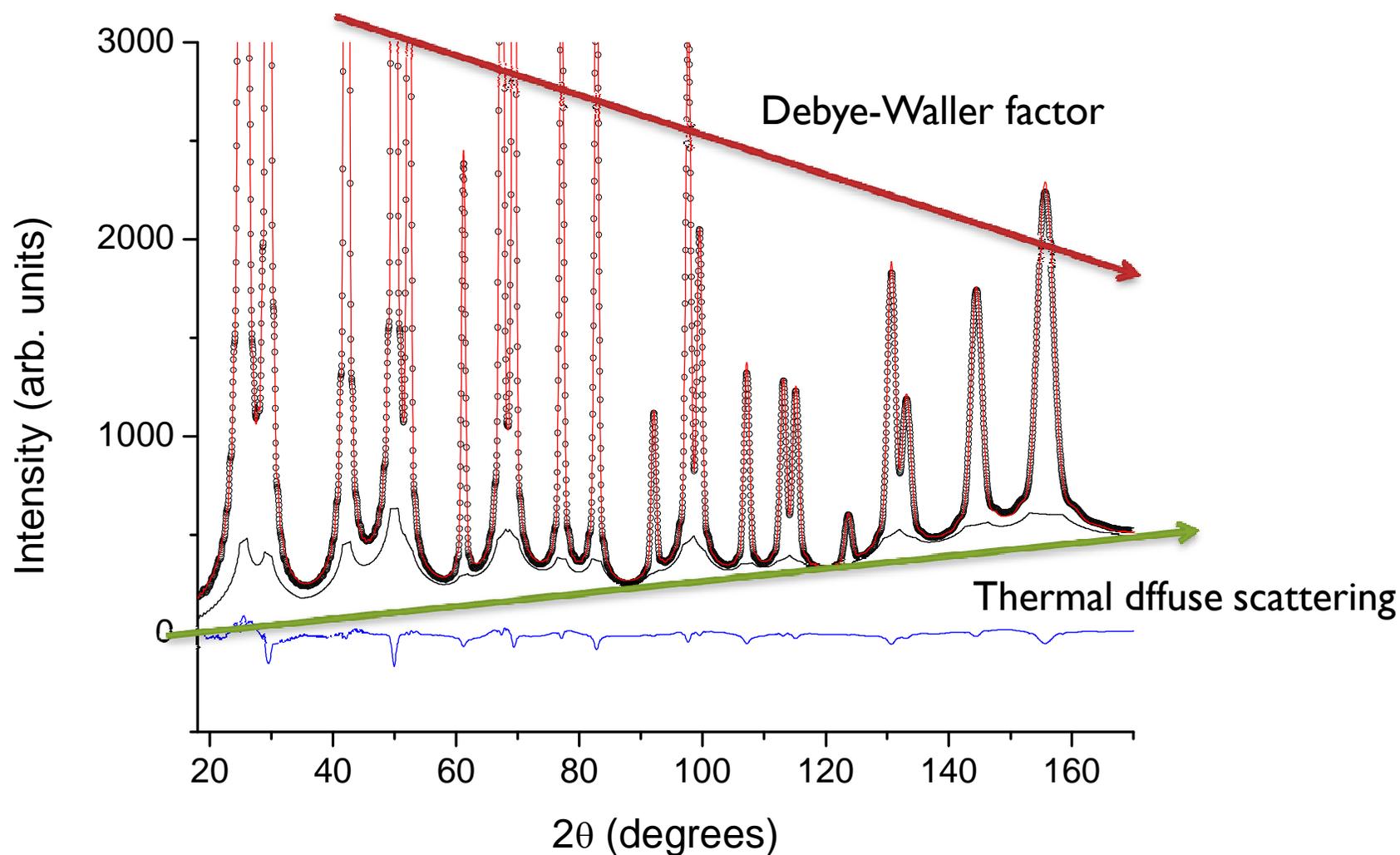
Accuracy in Powder Diffraction 4 – Gaithersburg 22-25 April 2013



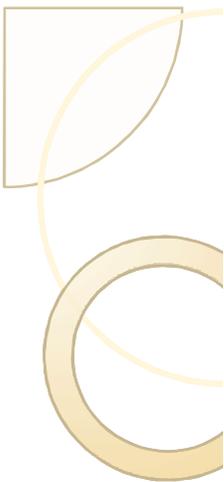


# What if the crystal is thermalised?

single 10 nm Cu domain, 300K, 1 Å data

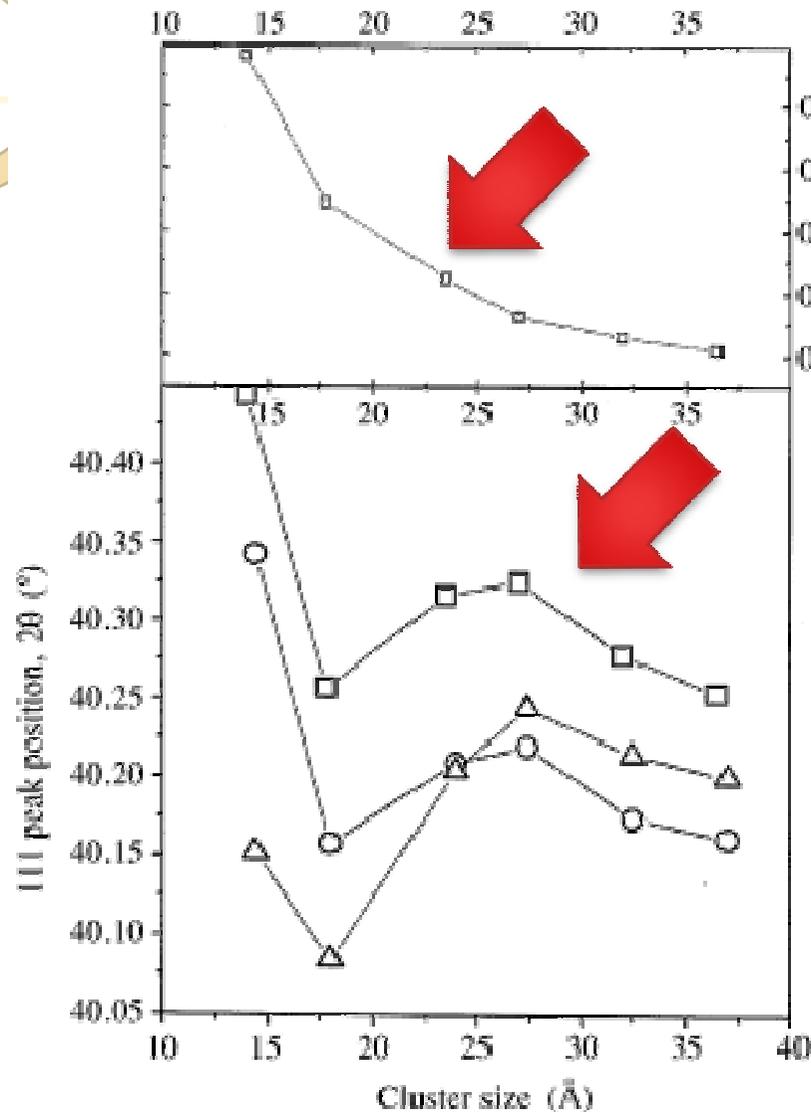


Refines to 9.96(5) with TDS and 9.71(3) without TDS



# Problems with cell parameter...

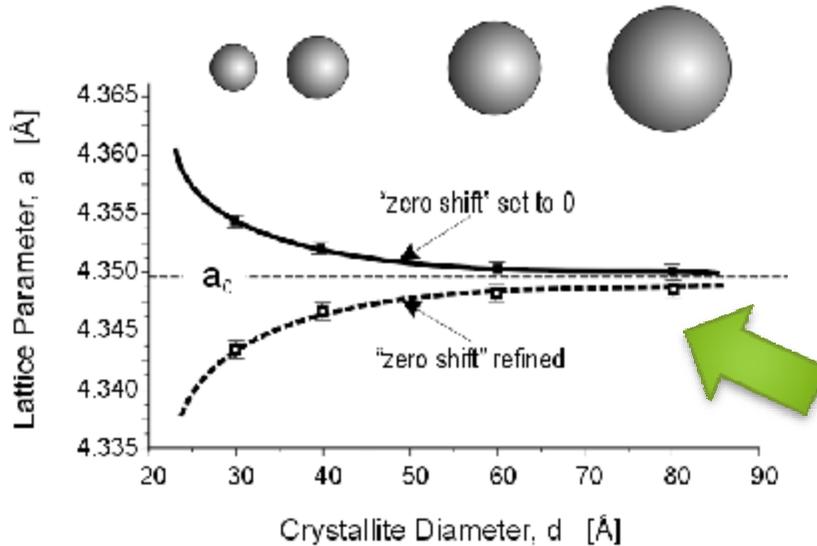
Z. Kaszkur, "Nanopowder diffraction analysis beyond the Bragg law applied to palladium", J.Appl. Cryst. (2000). 33, 87–94



**Figure 2**

Lower plot: the first diffraction maximum (apparent 111 peak) position ( $2\theta$  scale) of the calculated pattern (measured using Cu  $K\alpha$  X-ray radiation). The points correspond to: patterns calculated from the models of energy-relaxed cubooctahedra (squares), patterns calculated for the interior (all except outer shell) of the energy-relaxed next magic number cubooctahedra (see §3) (triangles), patterns calculated for the consecutive magic number cubooctahedra as an average over the MD run at 300 K (circles). All the peak positions are plotted *versus* approximate model cubooctahedron size (Å). Upper plot: the difference between the square and triangle points of the lower plot.

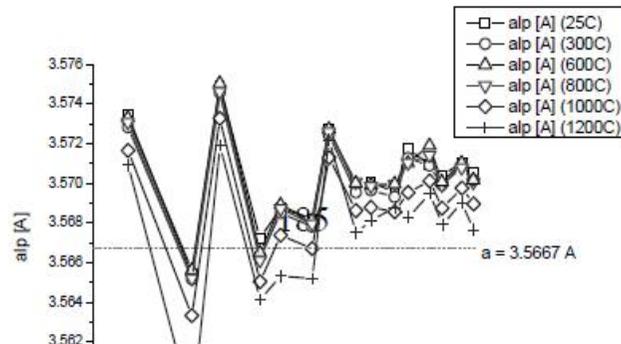
# .. found several times



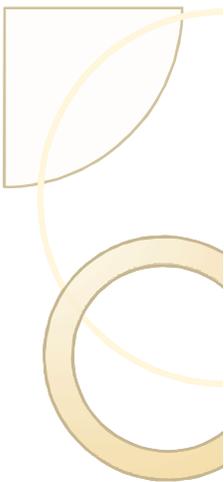
B. Palosz, E. Grzanka, S. Gierlotka, S. Stelmakh, et al. "Diffraction studies of nanocrystals: theory and experiment." Acta Physica Polonica Series A, 102 (2002) 57–82.

Apparent Lattice Parameter, *alp*

In reciprocal space, the Bragg Law is not valid anymore due to the fact that the coherent scattering length is of the same order of magnitude with the size of the crystals. To characterise such materials, the methodology of the apparent lattice parameter (*alp*) was introduced<sup>3</sup>. The *alp* analysis, see Fig.3, is showing that major changes take place at temperatures higher than 1000°C, similarly to the PDF analysis.

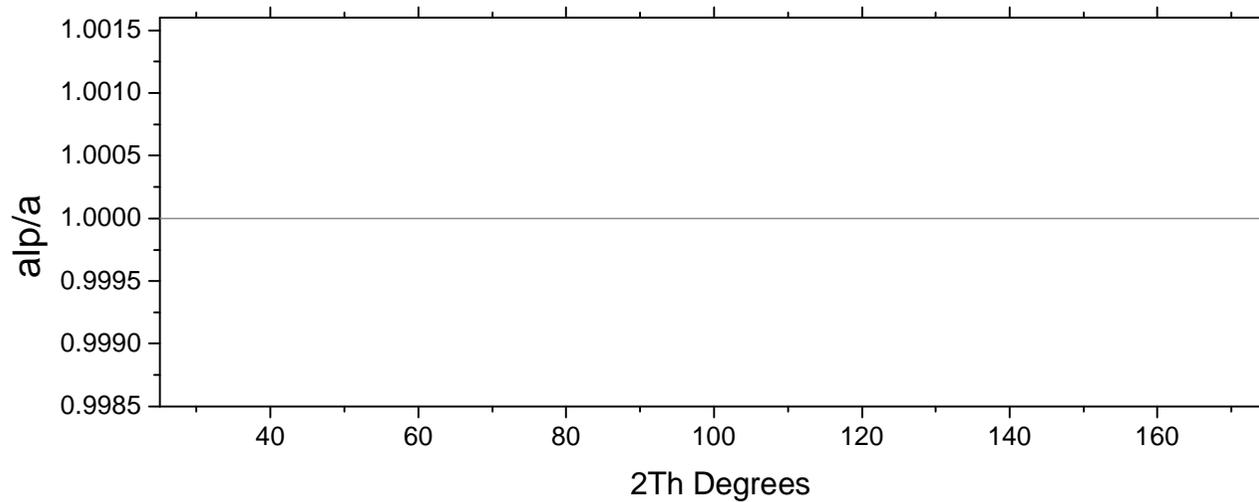
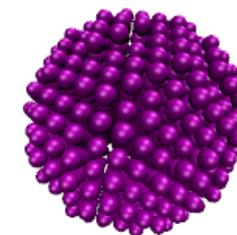
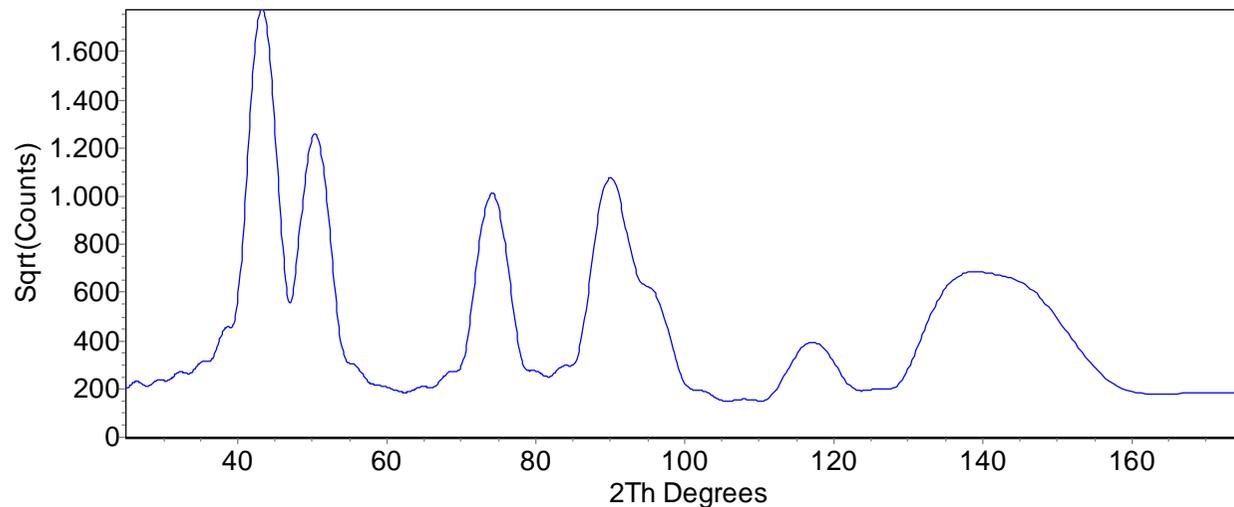


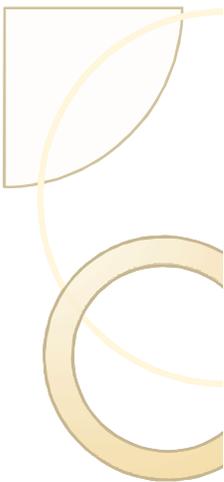
E. Grzanka, S.Stelmakh, C.Pantea, W. Zerda, B. Palosz, "Investigation of the relaxation of the nano- diamond surface in real and reciprocal spaces", 4-th Nanodiamond and Related Materials jointly with 6-th Diamond and Related Films, June 28th - July 1st, 2005, Zakopane, POLAND



# Testing for accuracy

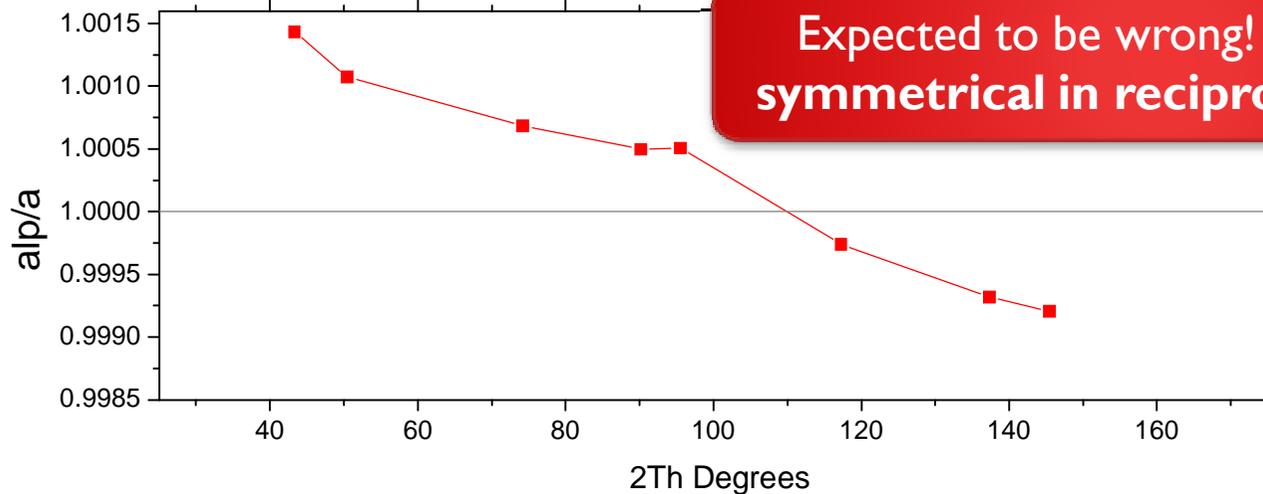
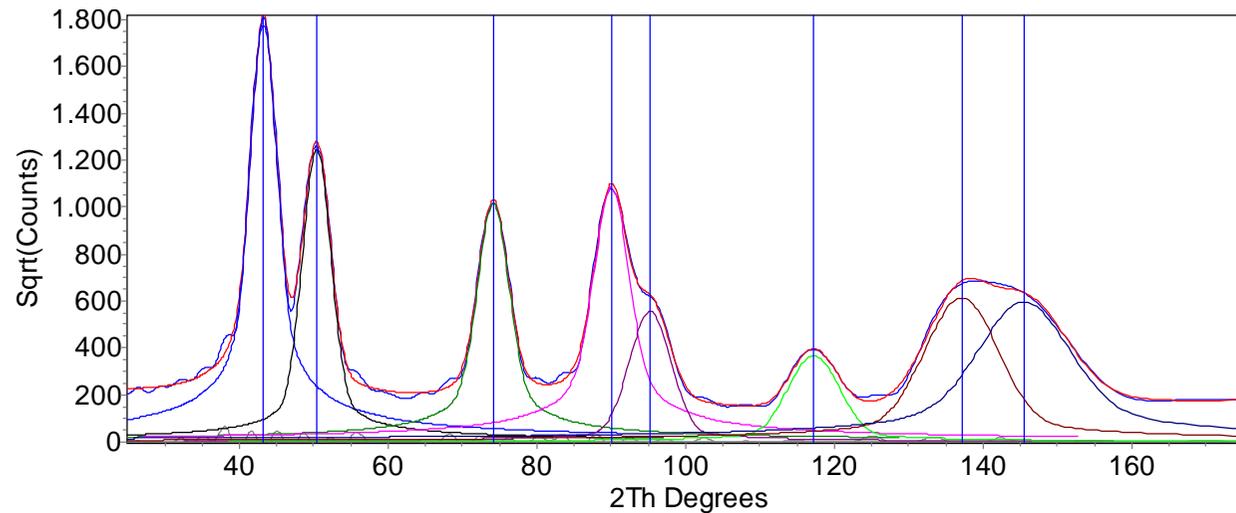
Calculation via Debye scattering formula, Cu domain 3 nm, 1202 atoms

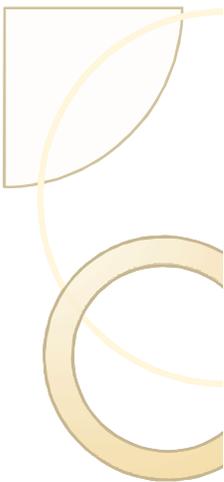




# The risk of fitting in $2\theta$

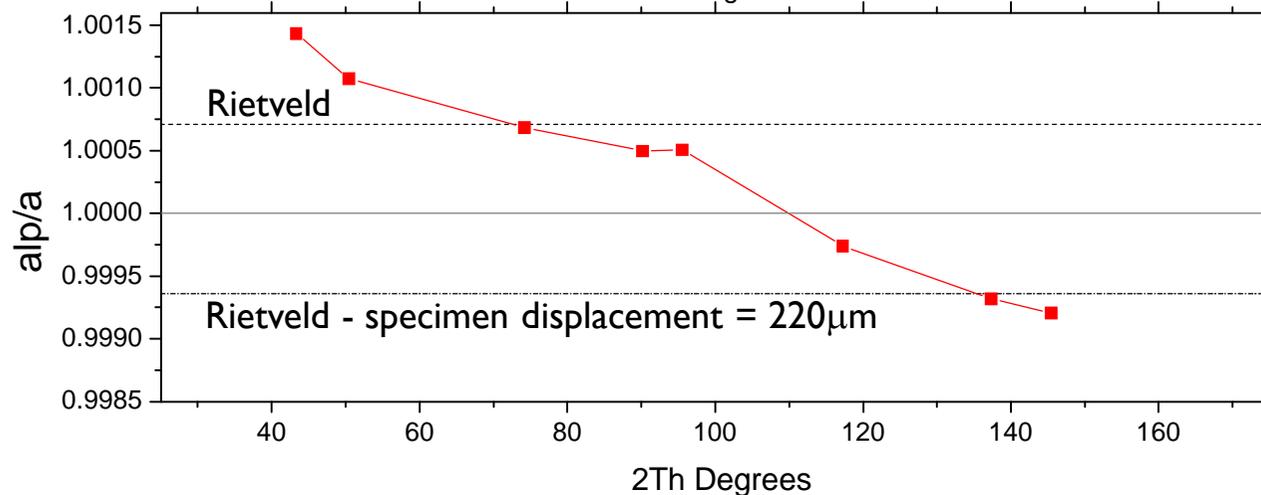
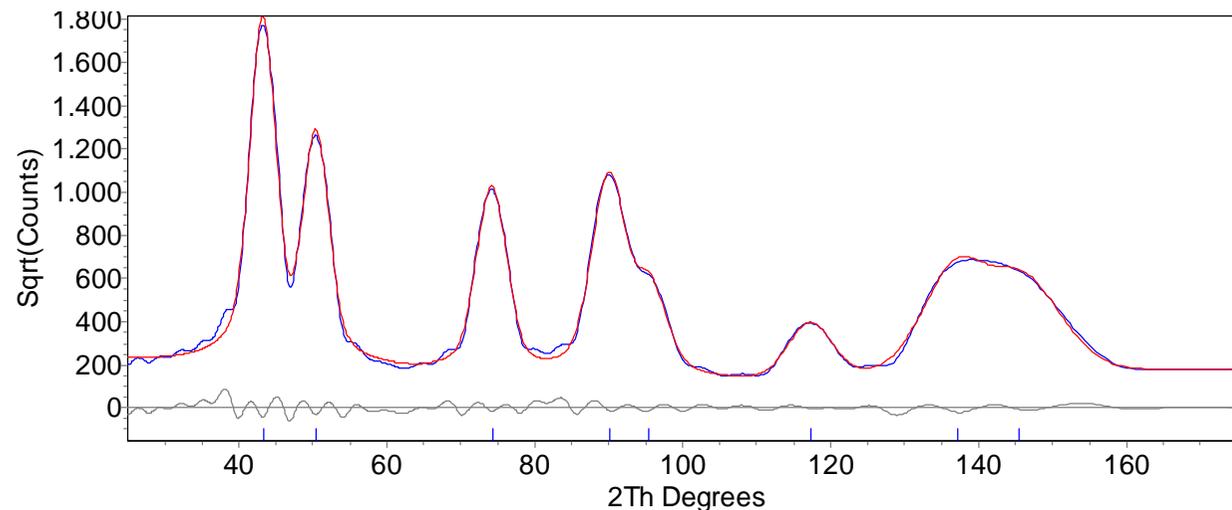
Single peak fitting in  $2\theta$  using pV functions



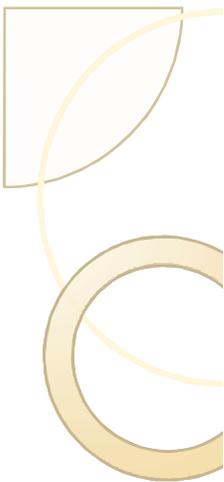


# Rietveld modelling: same story!

Rietveld refinement using FPA considering a specimen displacement

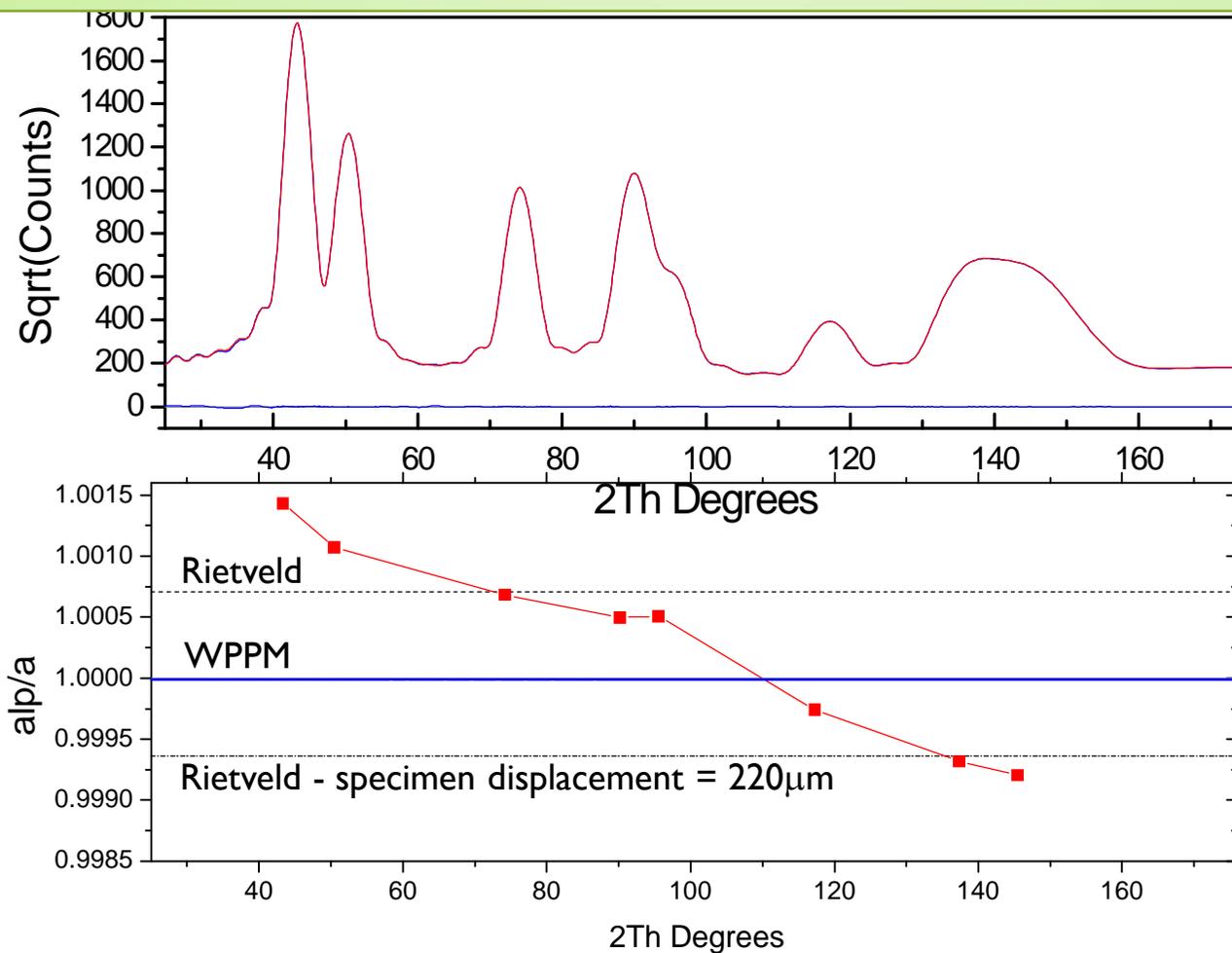


Why is it wrong? First hint: pV is symmetrical in the wrong space. But not just that...



# Whole Powder Pattern Modelling

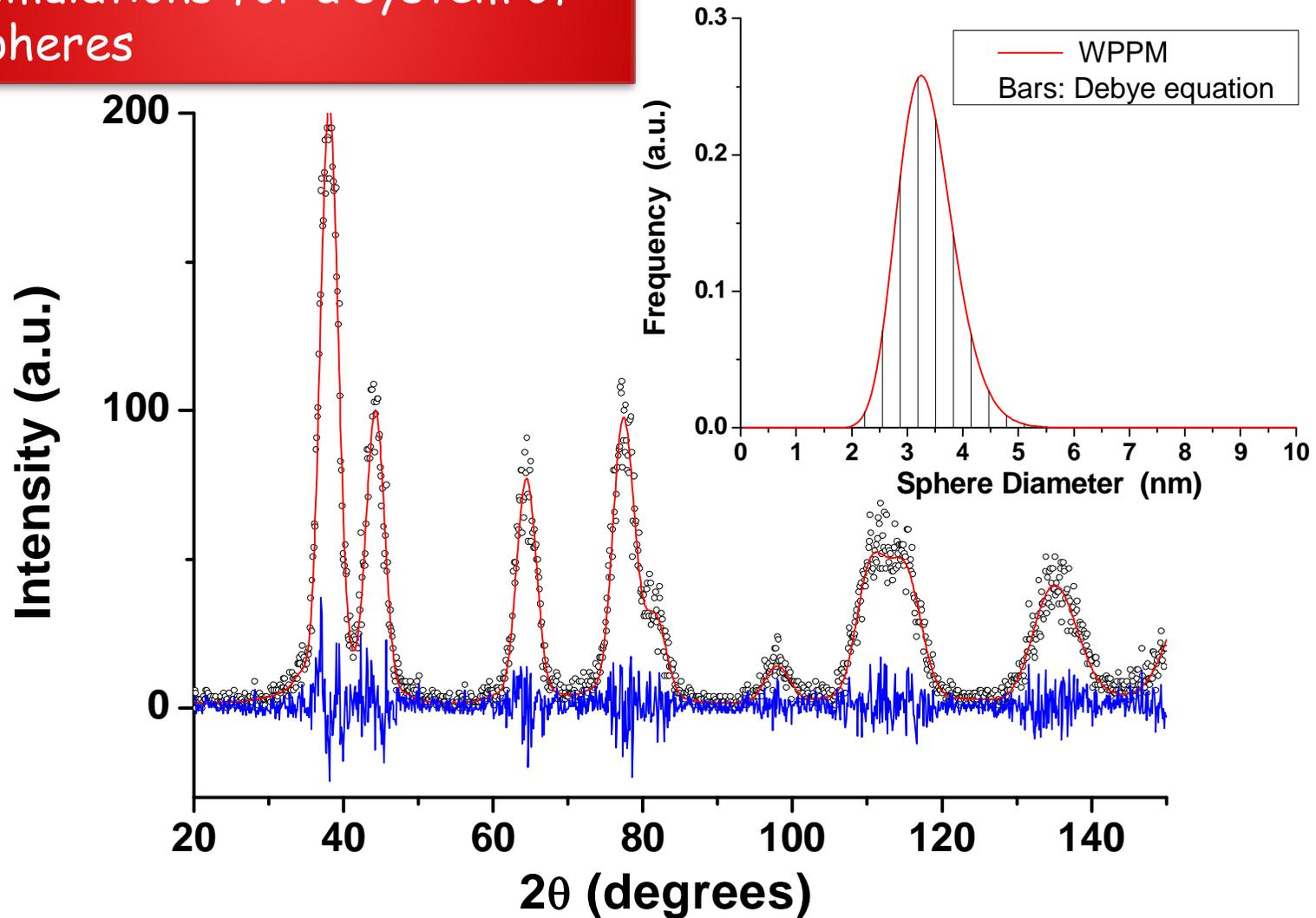
“Ab initio” using fixed cell parameter, Patterson (1939) formula, symmetric profiles in Q, correct Lorentz factor and addition of SAXS tail



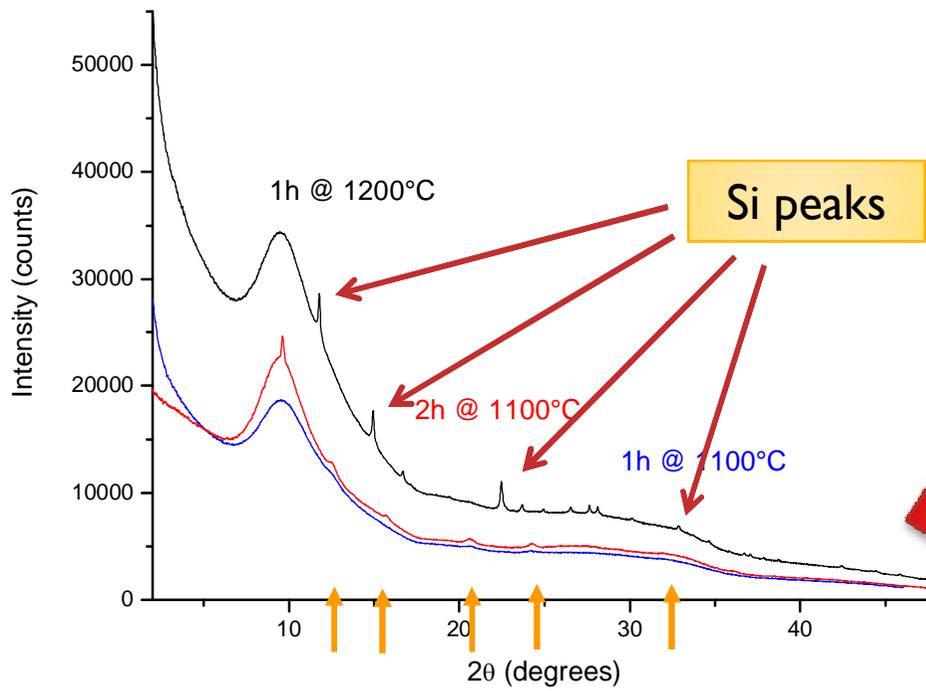
Apparent lattice parameter can therefore be an artefact!

# WPPM versus Debye equation

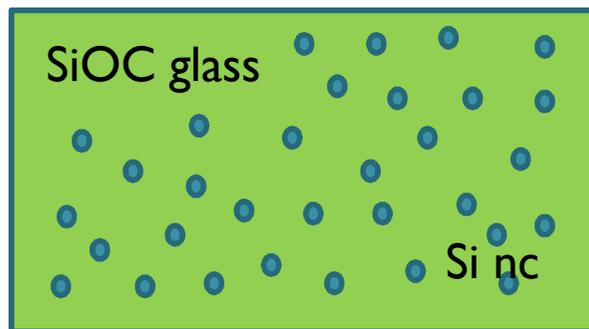
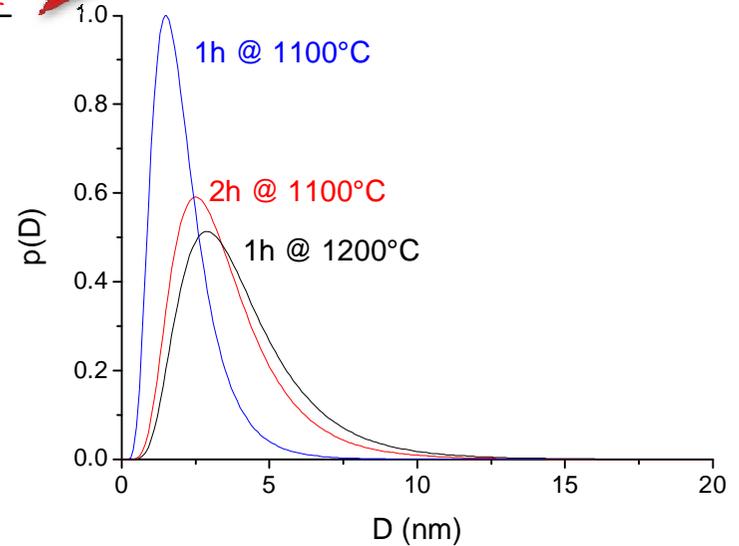
What is the limit of WPPM ?  
Simulations for a system of spheres



# Si-nc in oxycarbide glass



Microstructure extraction via WPPM

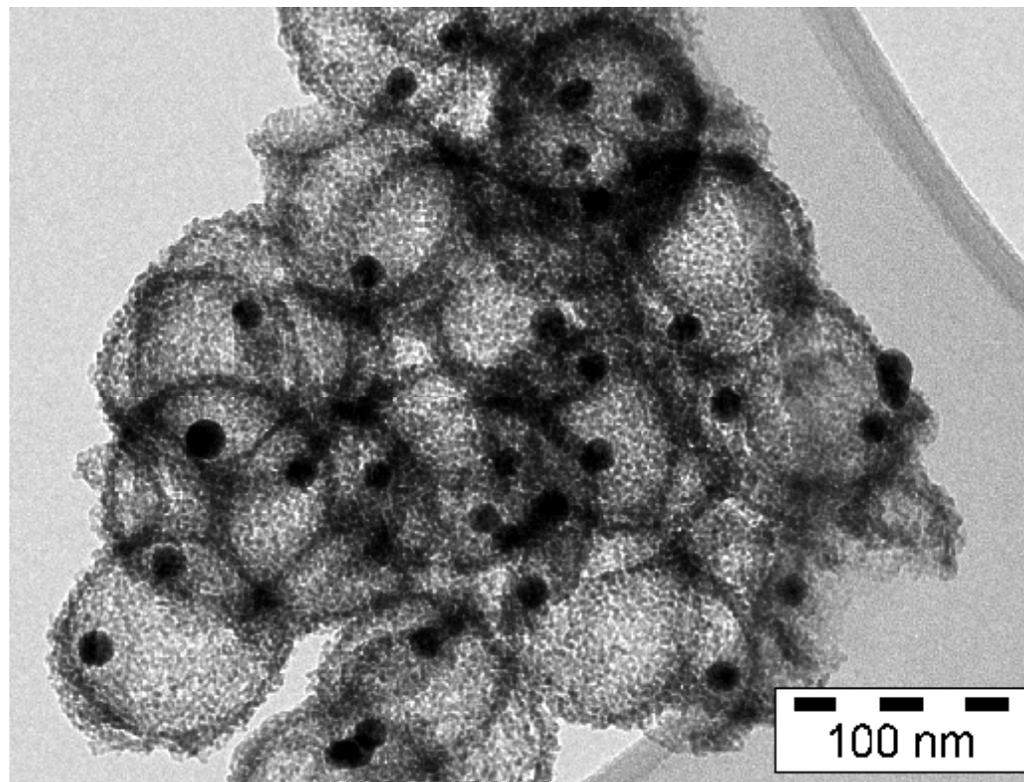
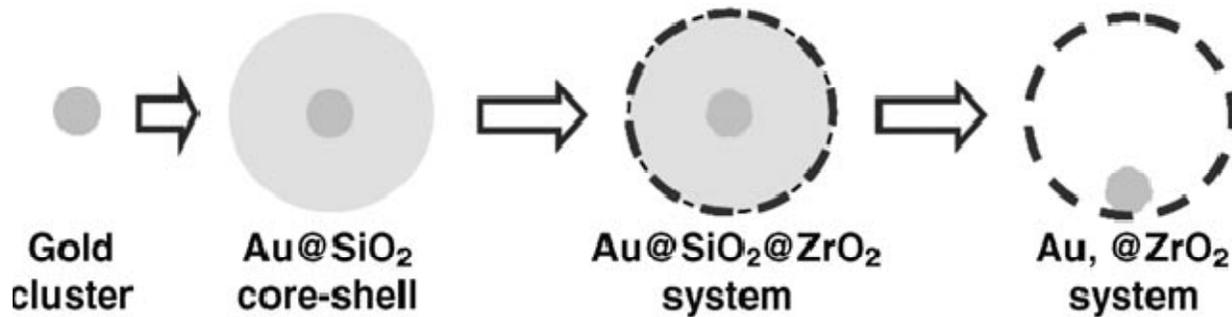




# **EXAMPLE: CATALYSTS**

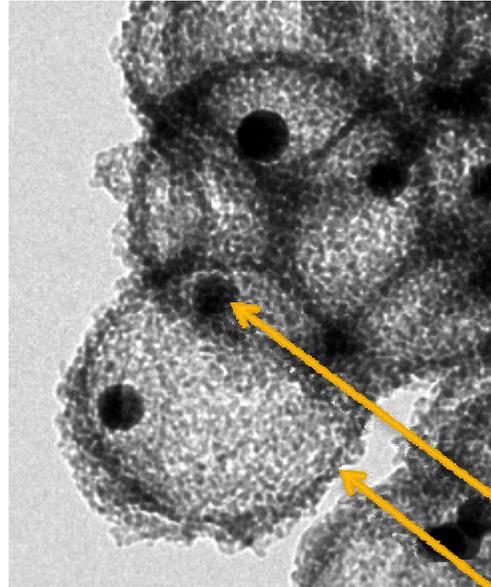


# Au@ZrO<sub>2</sub> yolk-shell catalysts



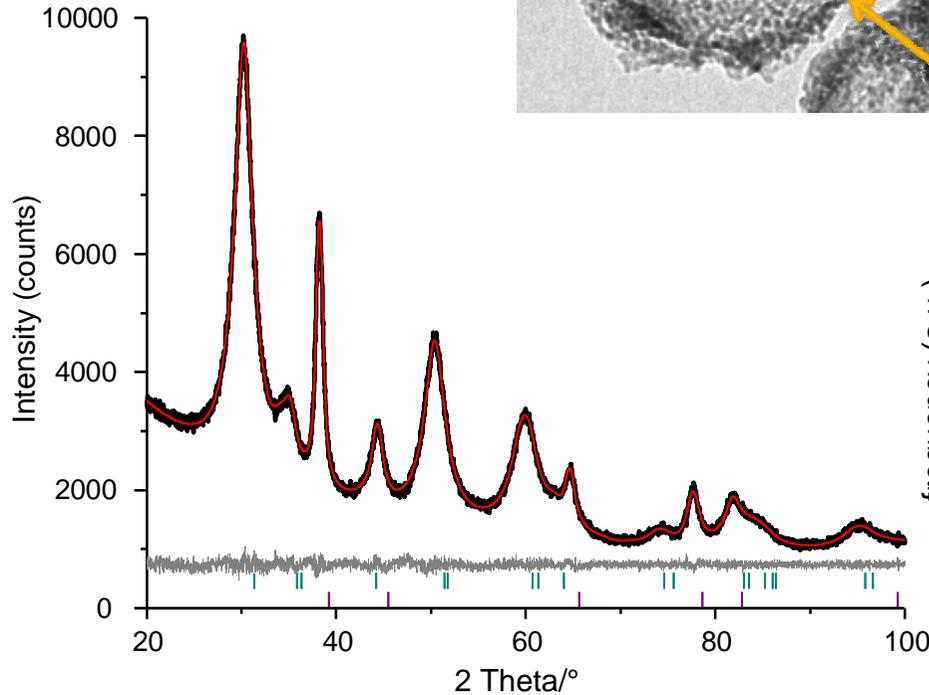
Complex system,  
hard to characterize  
with the TEM

# Au@ZrO<sub>2</sub> yolk-shell catalysts

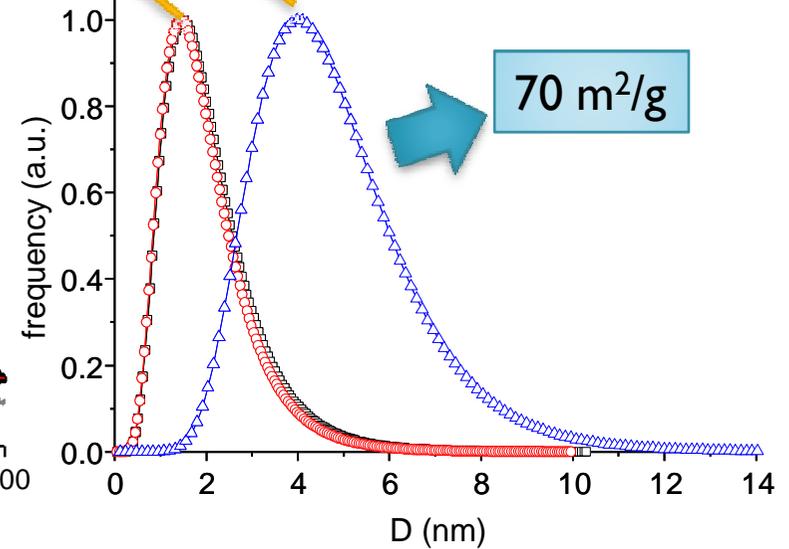


Nanocrystalline Au  
inside a cage of porous  
nanocrystalline ZrO<sub>2</sub>

WPPM for phases  
and size distribution

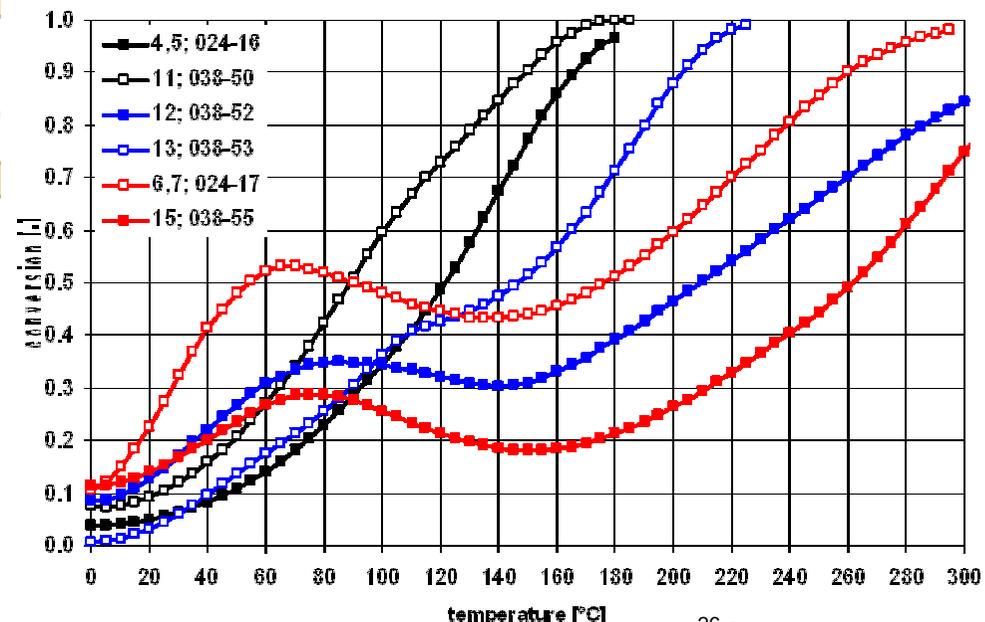


Phase-selective  
specific area calculation!



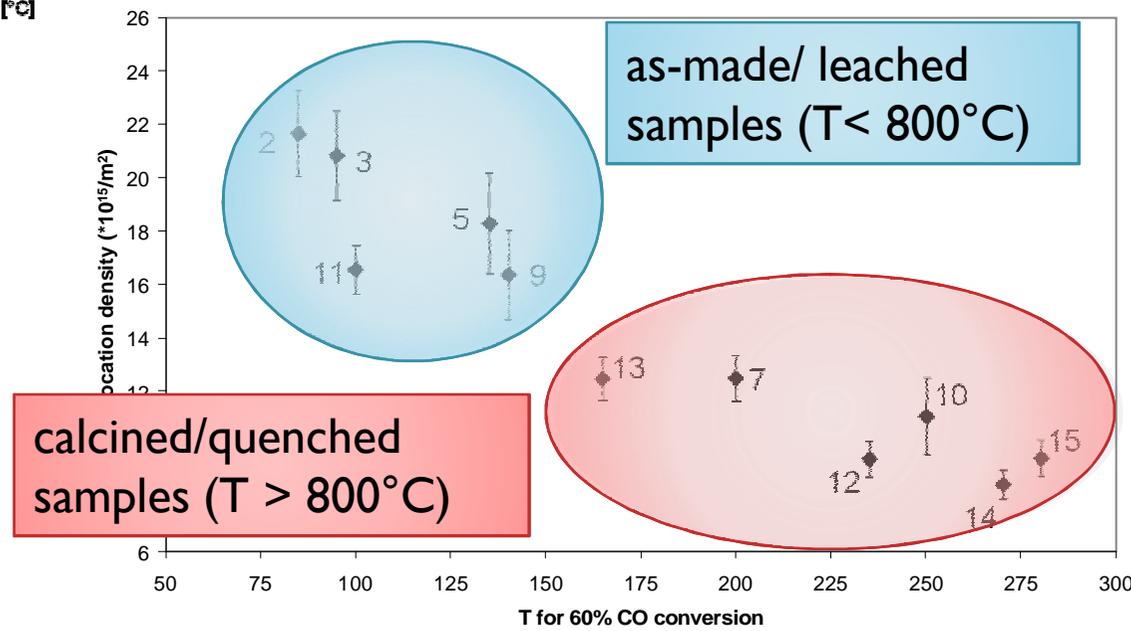


# Au@ZrO<sub>2</sub> yolk-shell catalysts



CO conversion as a function of T for:  
 11: as made;  
 5: leached  
 13: heated to 800 °C and slow cooling  
 7: heated to 900 °C and quenched  
 12: heated to 900 °C and slow cooling  
 15: heated to 900 °C and quenched

Defects outcrop  
 increase the activity of  
 the catalyst!!

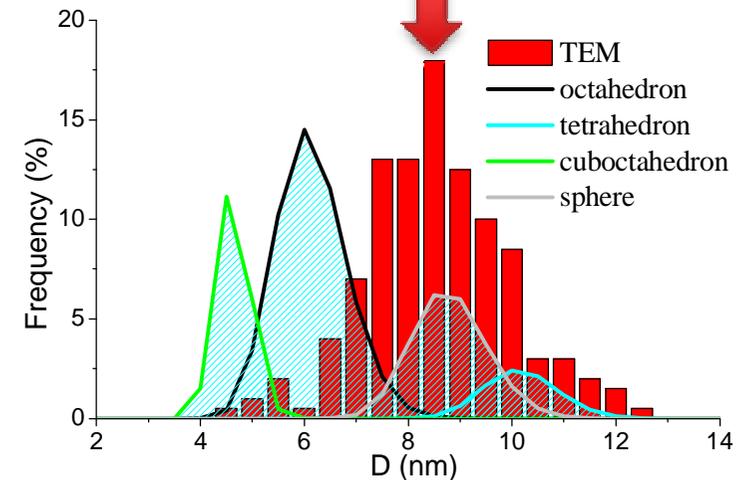
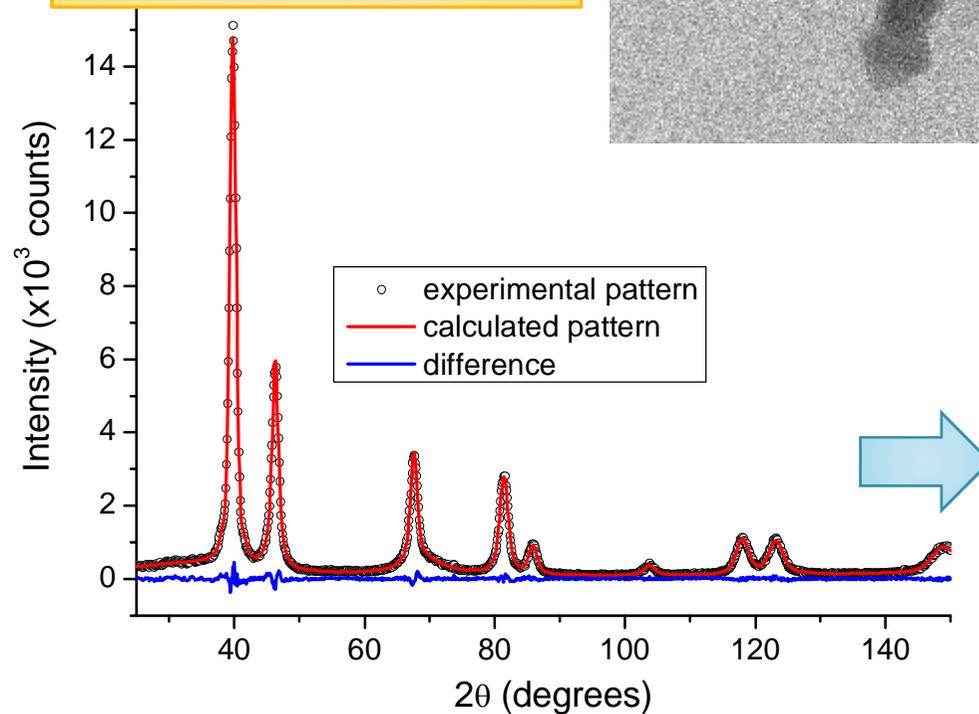
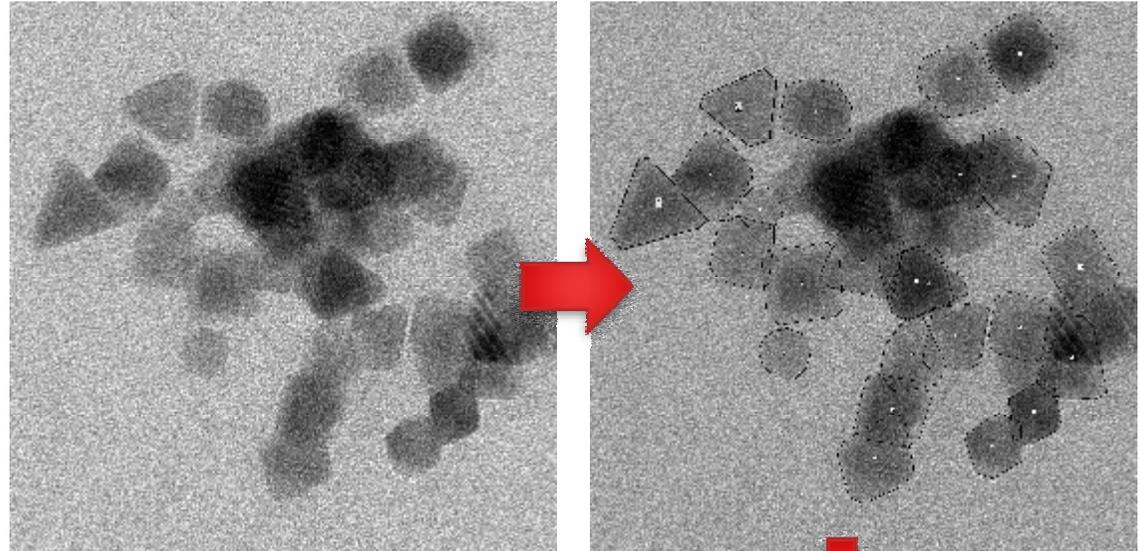


# Pt nanocatalysts

Nano-Pt by reducing  $\text{H}_2\text{PtCl}_6$  using  $\text{H}_2$  in presence of sodium polyacrylate

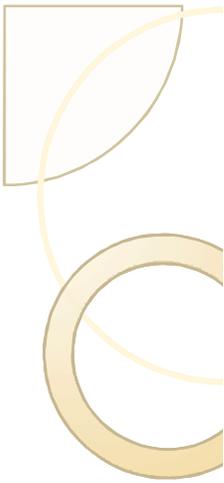
Soft chemistry employed to control the shape of the particles

WPPM to check the distribution of size and shapes

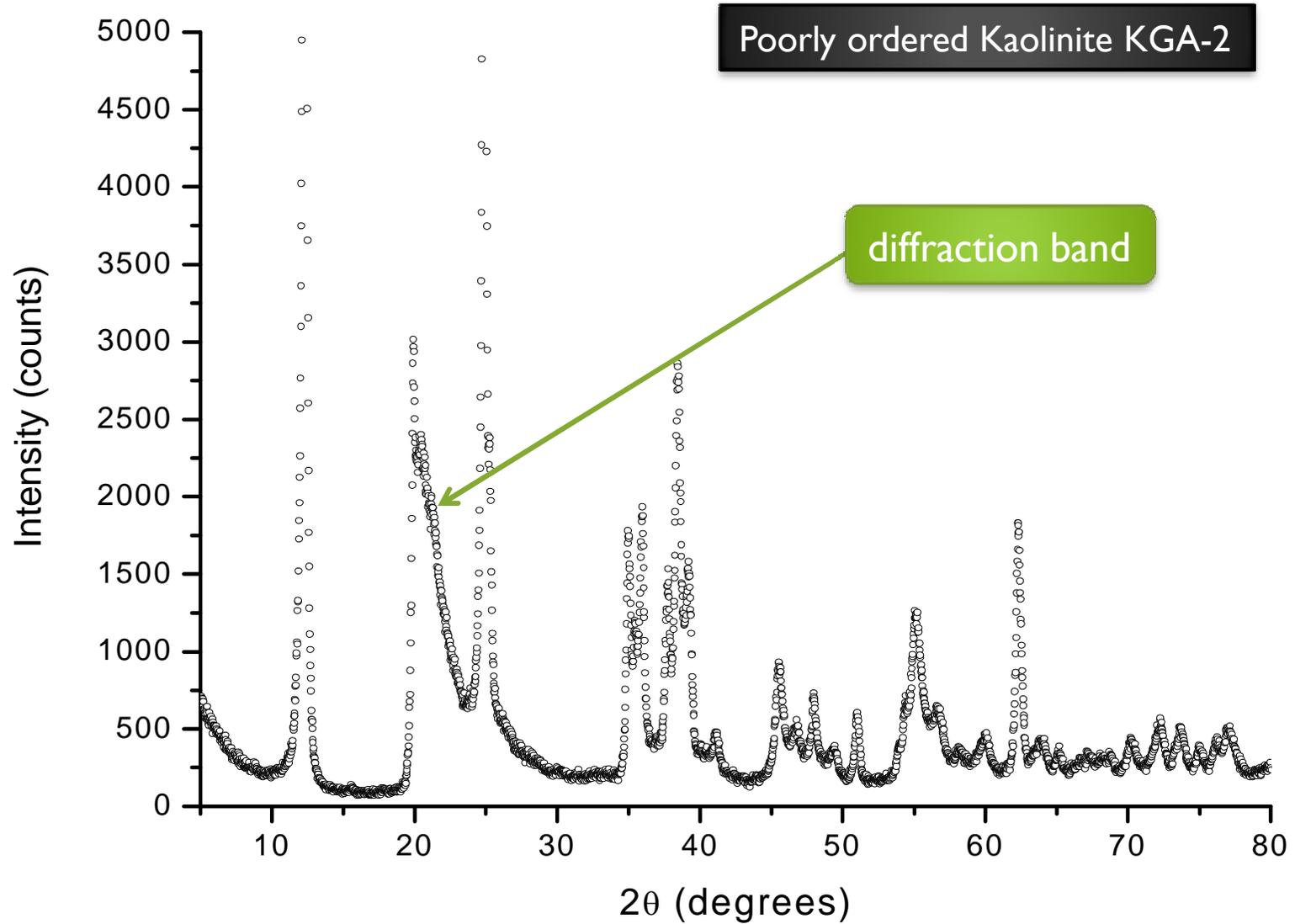




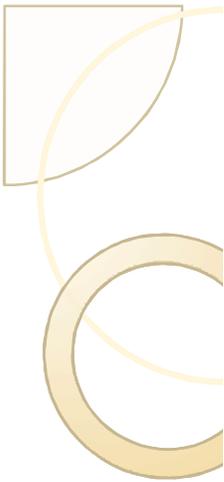
# **CONCLUDING REMARKS**



# (yet) Hard-to-treat case



WPPM cannot solve all cases: it deals with "well behaving" defects only



# Concluding remarks/caveats

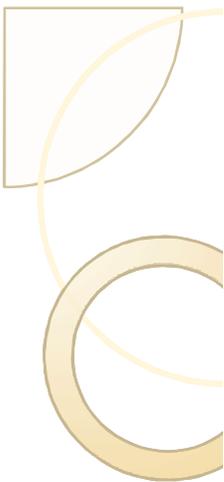
Accuracy in line profile analysis has definitely improved in the last years

Good fit does not always mean good/accurate result

Fit the models on the measured data (not viceversa)

Use the quick and dirty tools for comparison and a WPPM-type approach for more quantitative studies

**NEVER EVER** use any result from microstructure analysis without knowing what you are doing / how you obtained it!



# Conclusions

My drawing was not a picture of a hat. It was a picture of a boa constrictor digesting an elephant. But since the grown-ups were not able to understand it, I made another drawing: I drew the inside of the boa constrictor, so that the grown-ups could see it clearly.

**They always need to have things explained.**

